

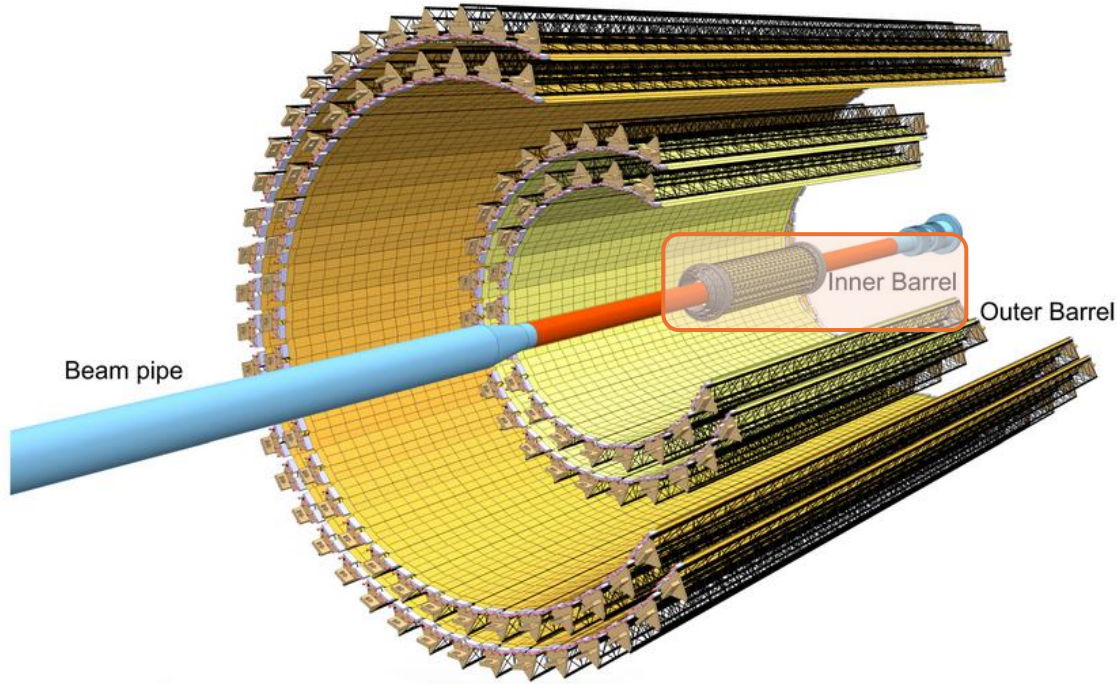


Development of the MOSAIX chip for the ALICE ITS3 upgrade

TWEPP, Glasgow, Scotland. October 2nd 2024

Pedro Vicente Leitao, CERN, Switzerland

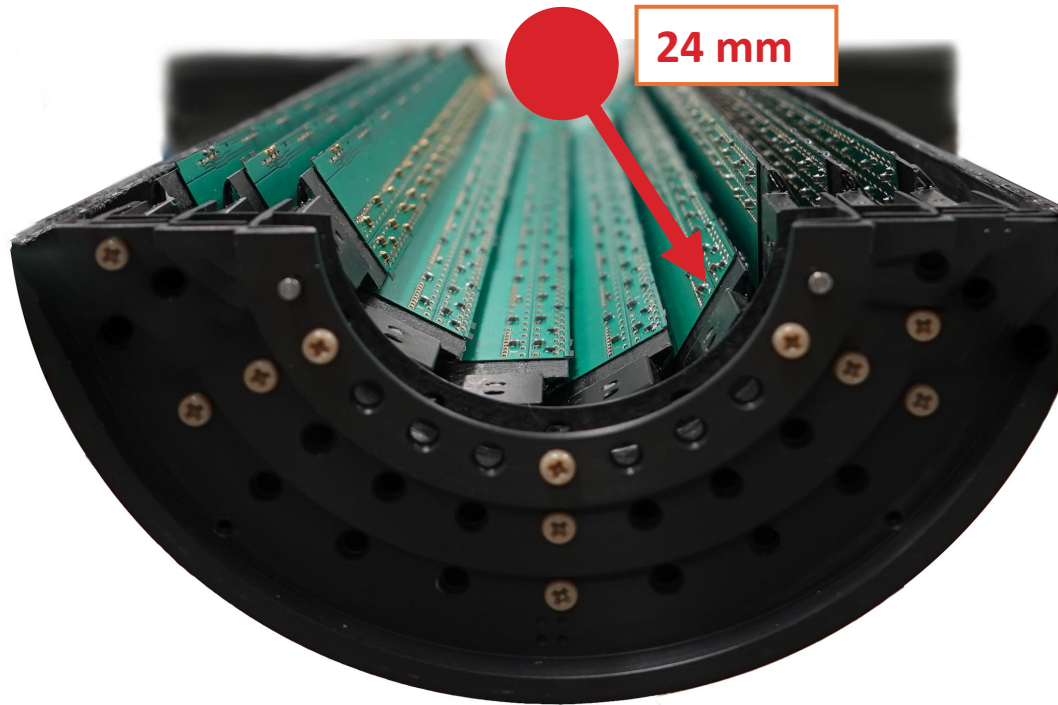
ALICE ITS



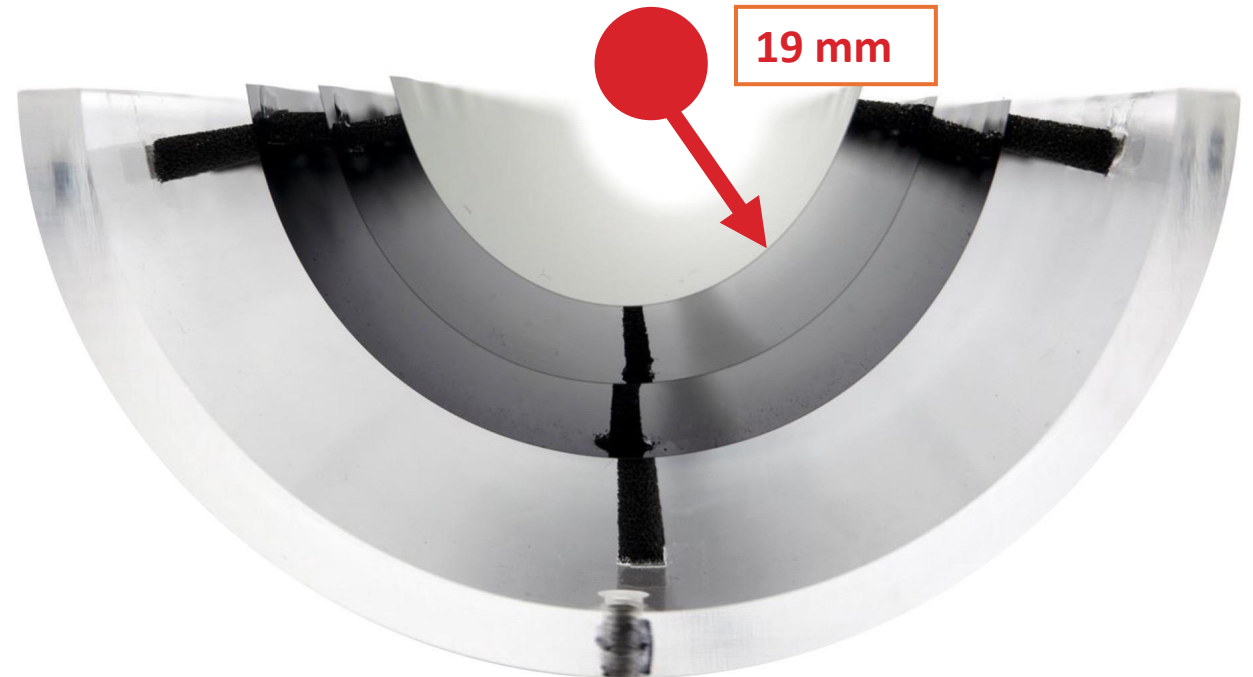
ALICE ITS2
half inner barrel

What can we do better?

Everything is on-chip: silicon-only pixel detector



24 mm from the beam pipe
0.35 % X_0 per layer

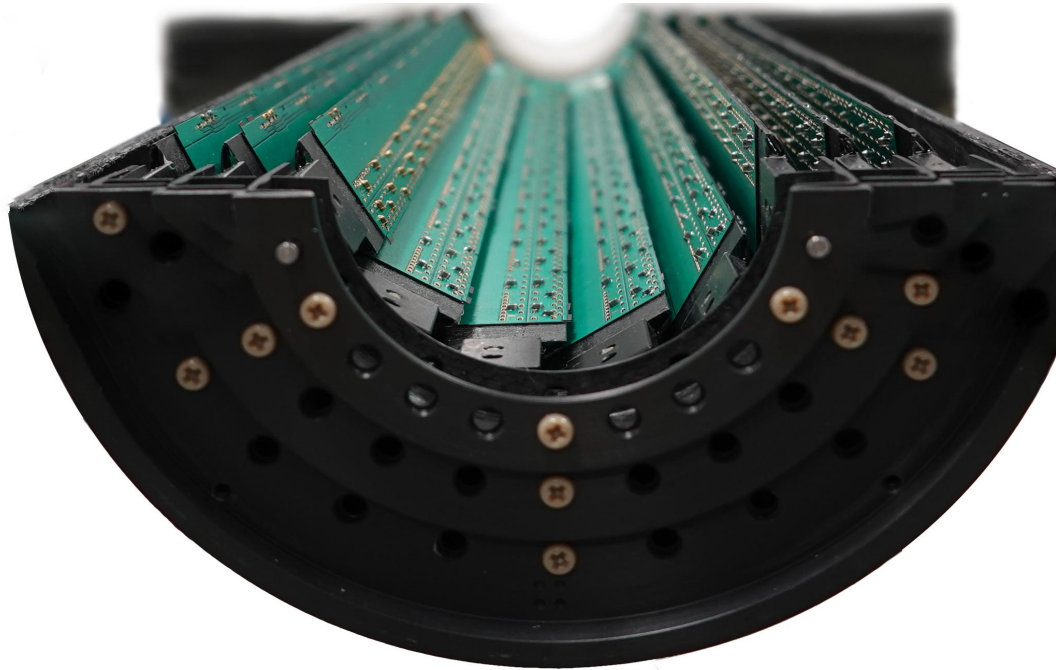


19 mm from the beam pipe
0.07 % X_0 per layer

What are the challenges?

Everything is on-chip

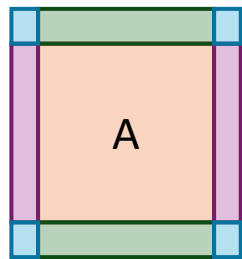
- Power distribution on-chip
- Data communication on-chip
- No active cooling
- Manufacturing defects



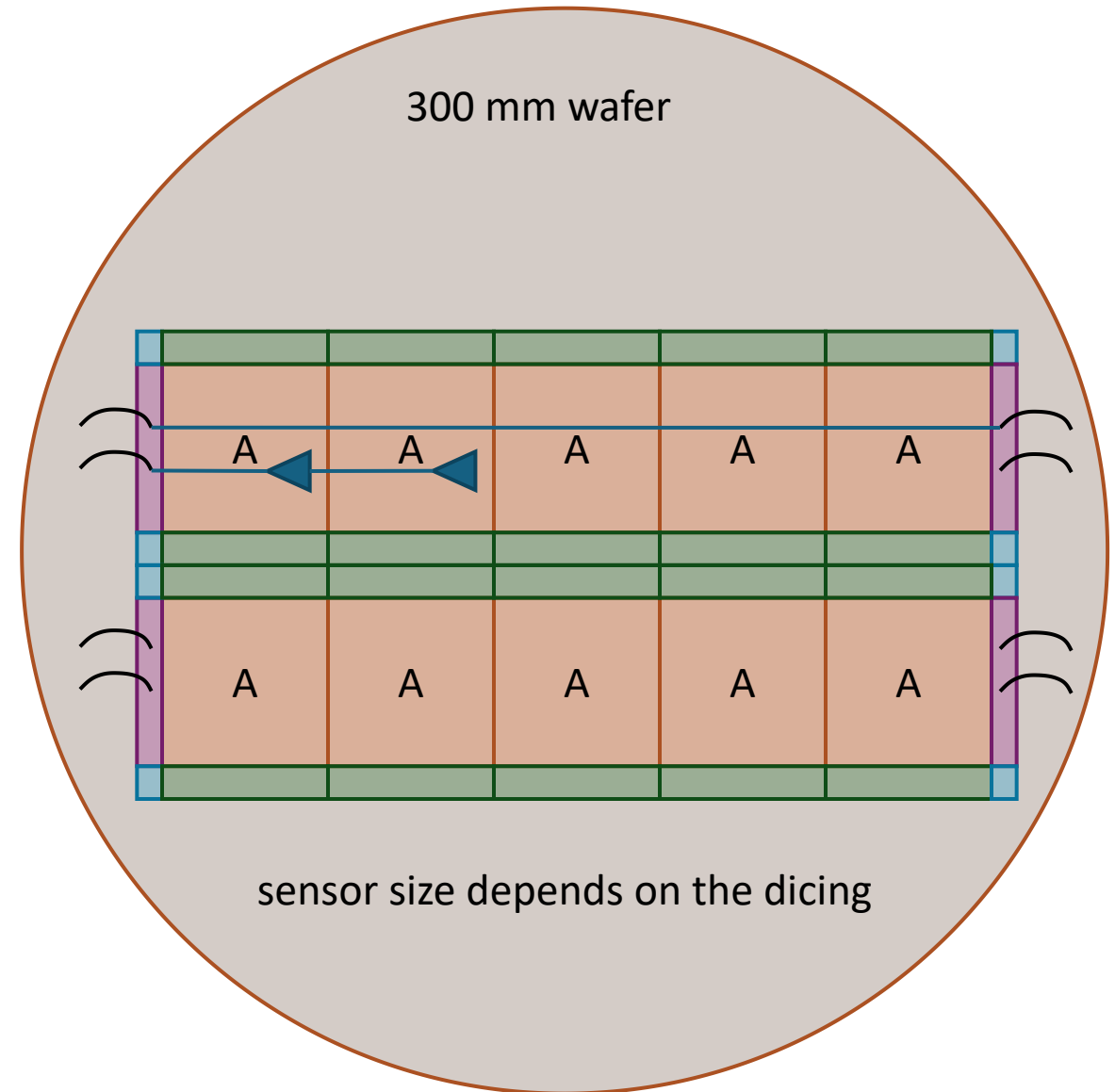
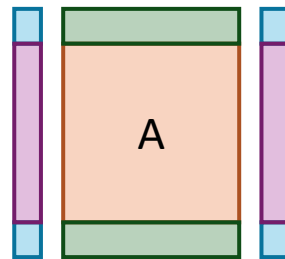
Design a large area silicon-only bent pixel detector

How to design a wafer scale bent pixel detector?

Max reticle size



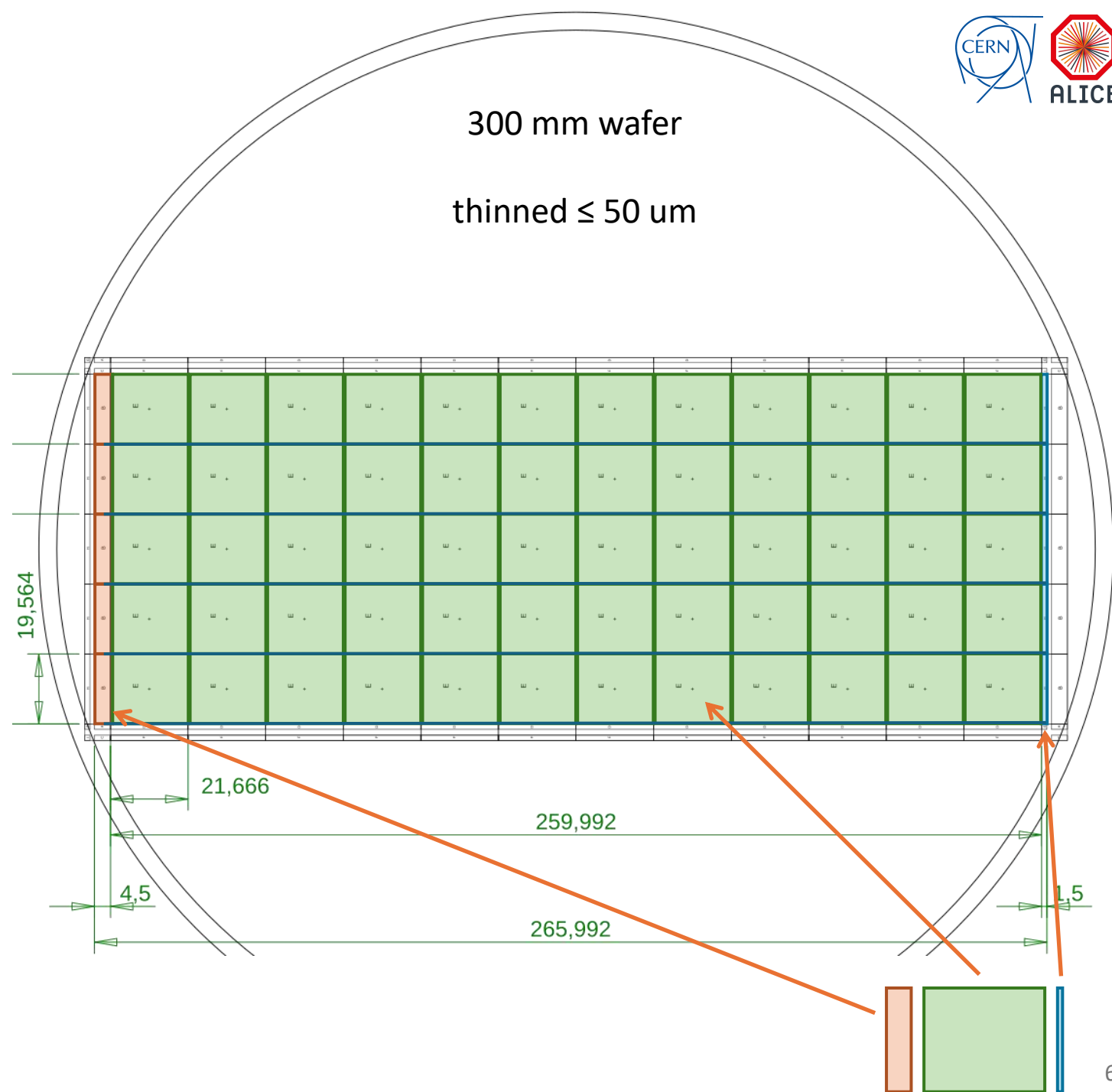
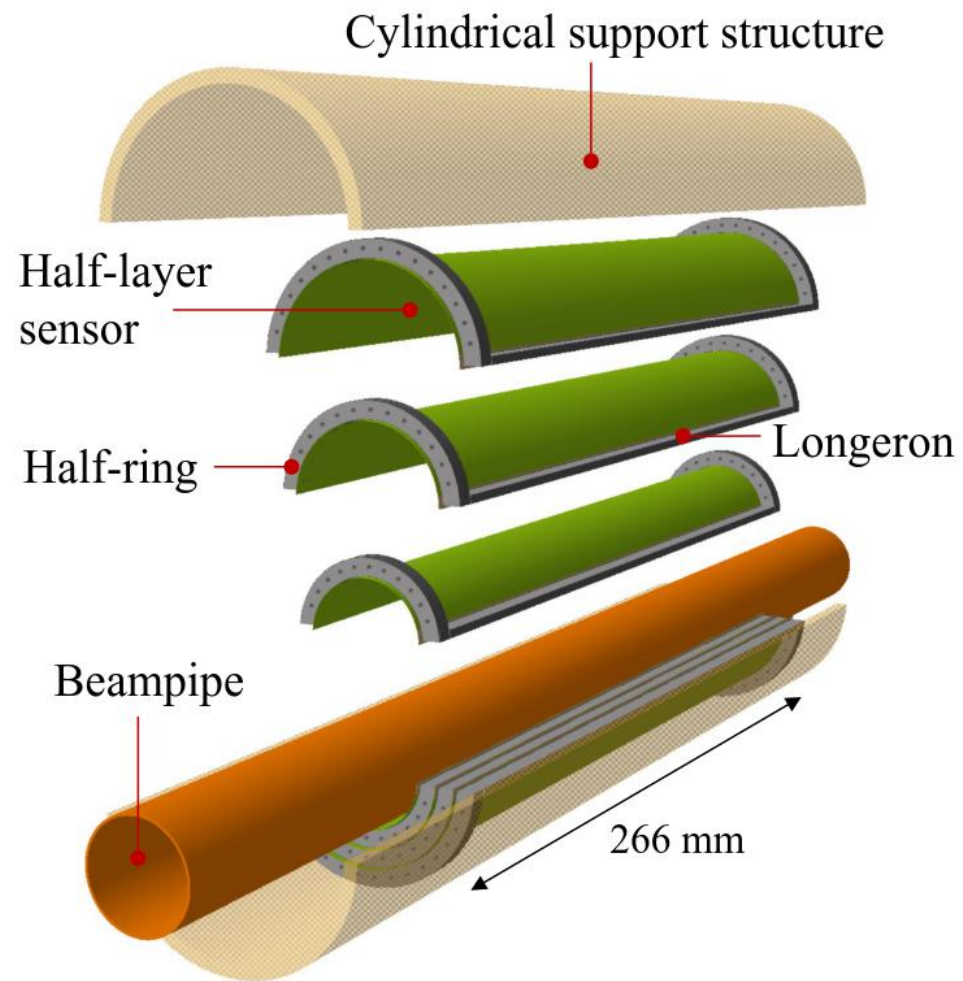
split design



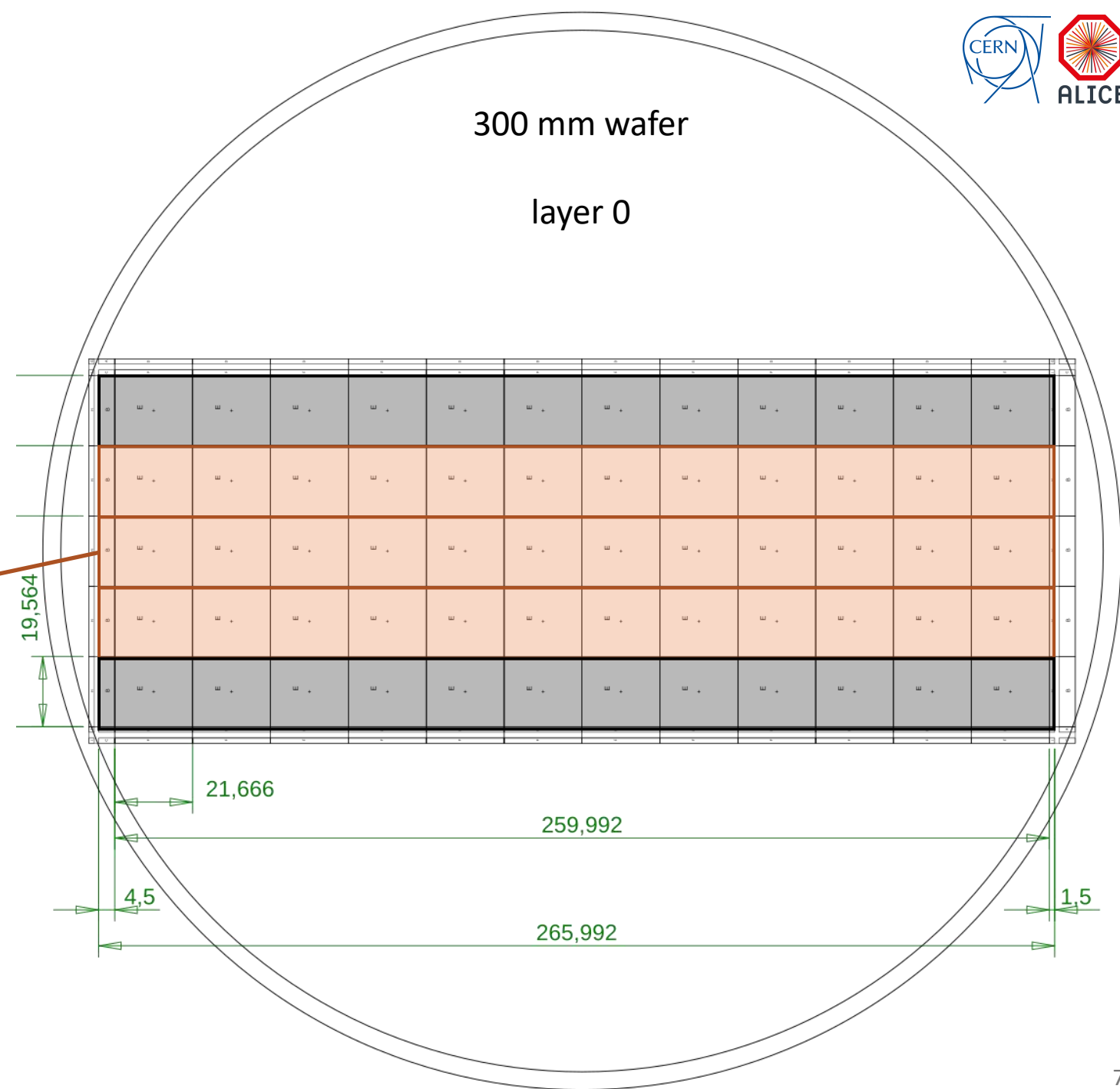
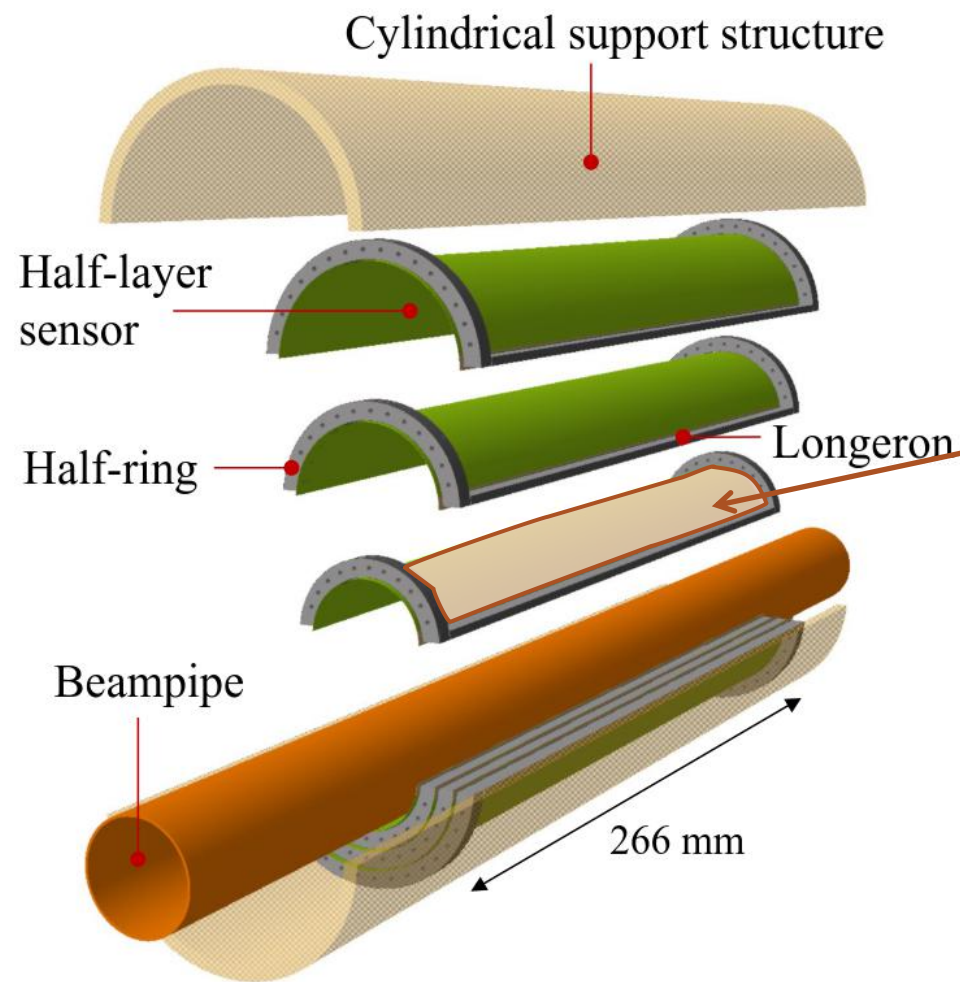
Only possible if the technology allows stitching

A = sensitive area

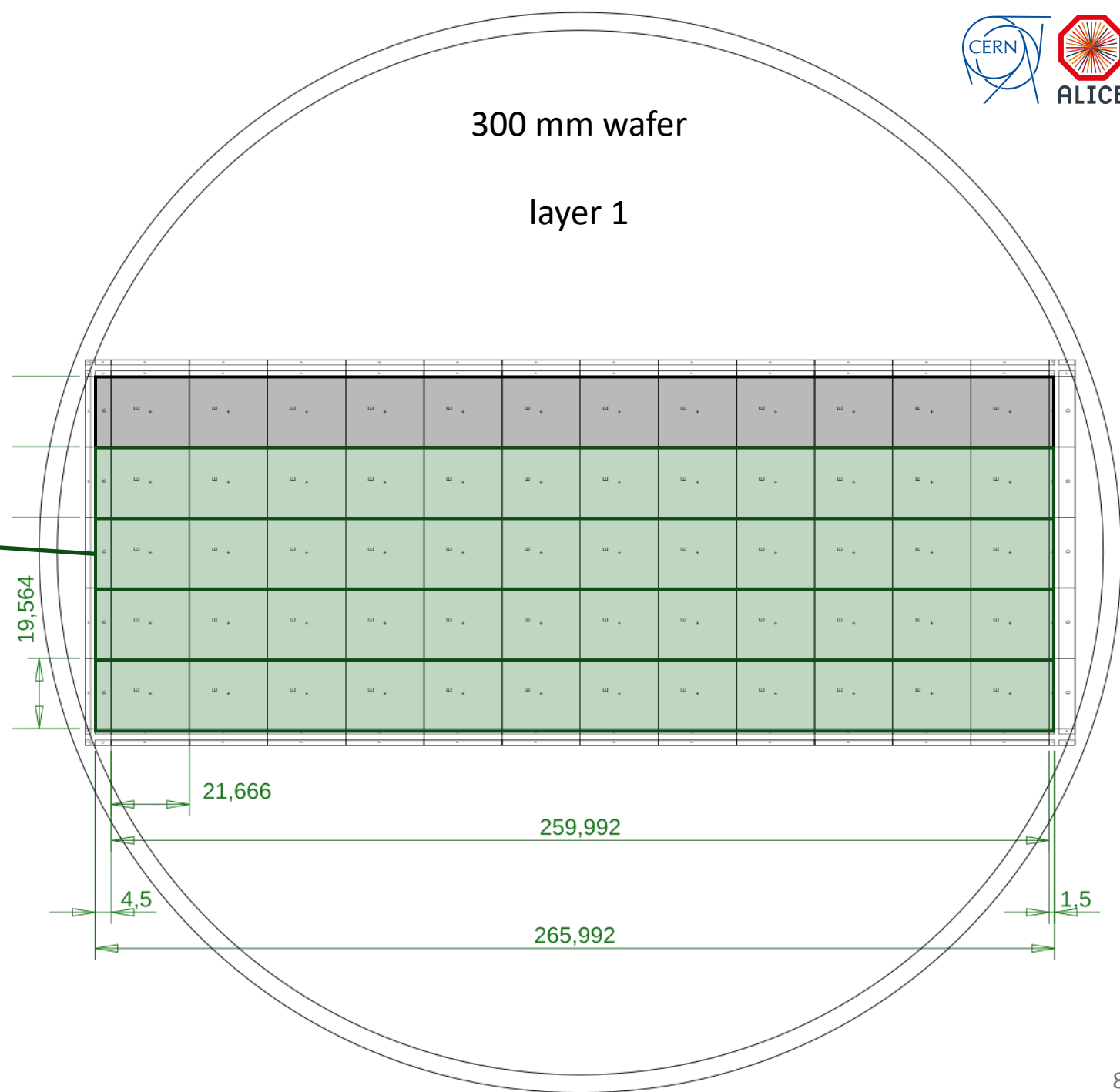
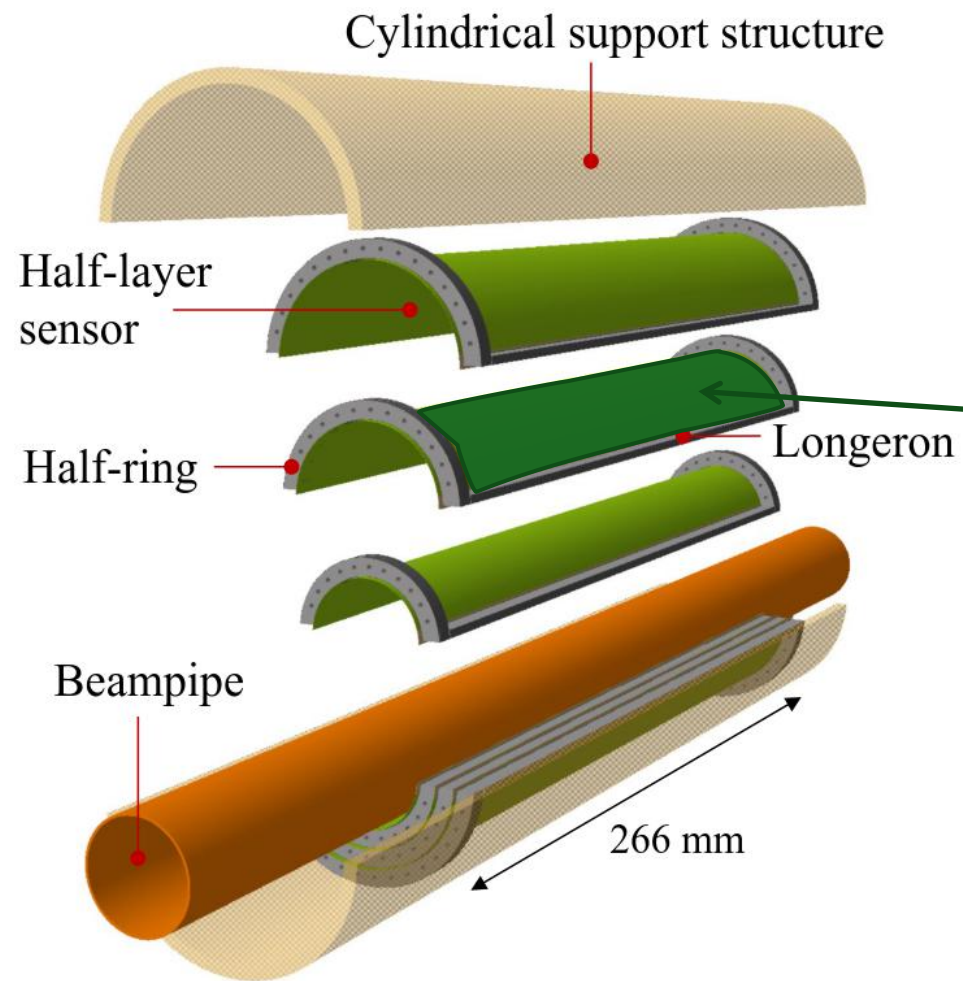
ITS3 detector



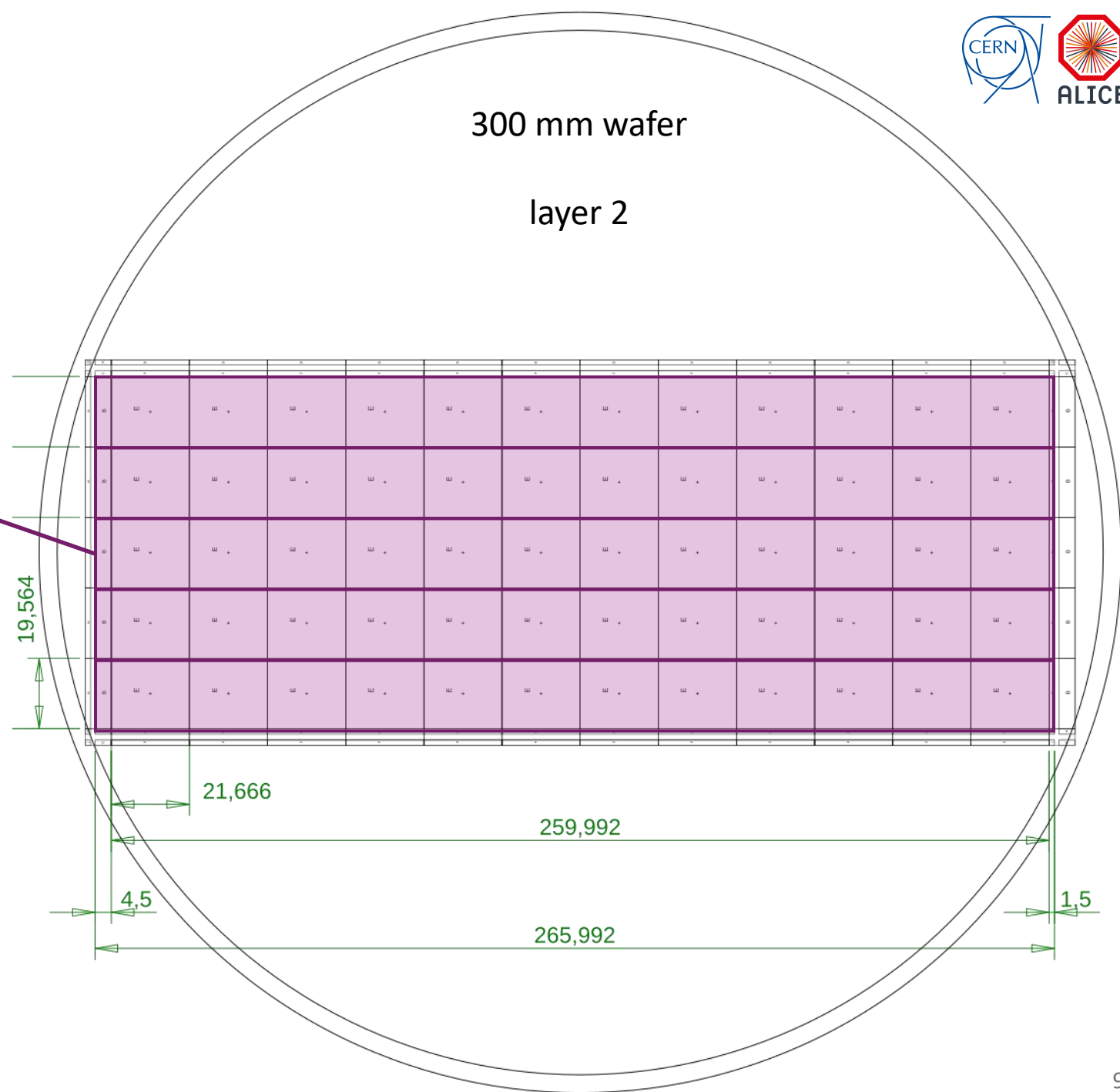
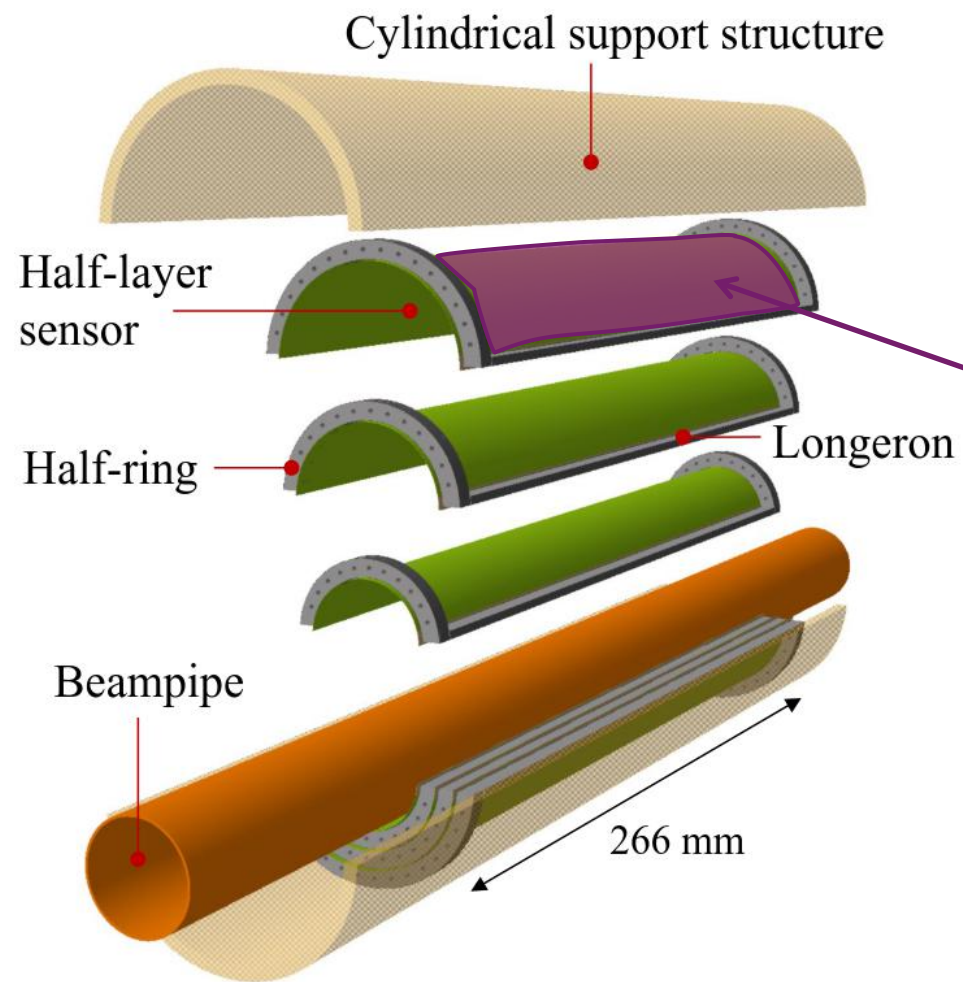
ITS3 detector



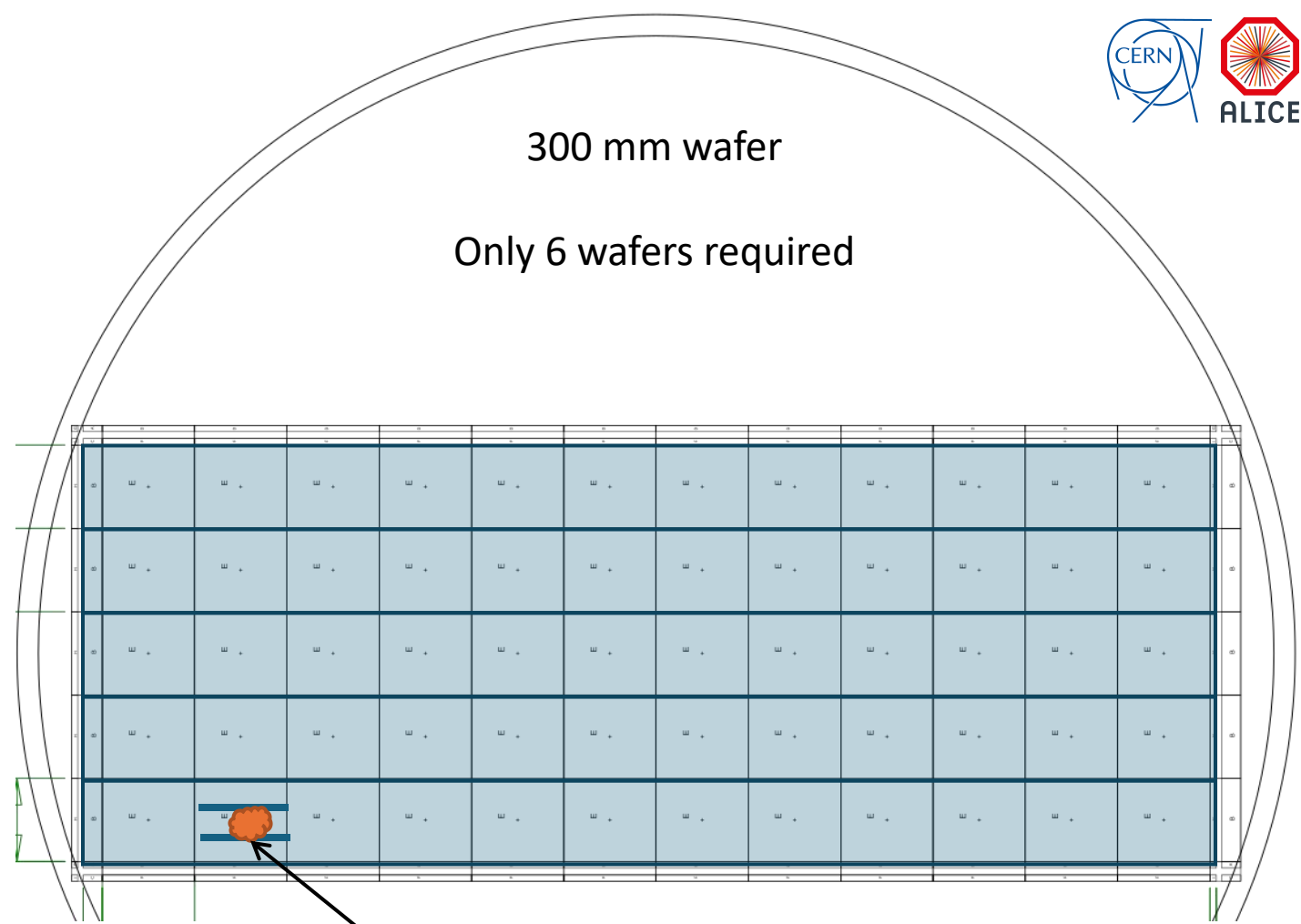
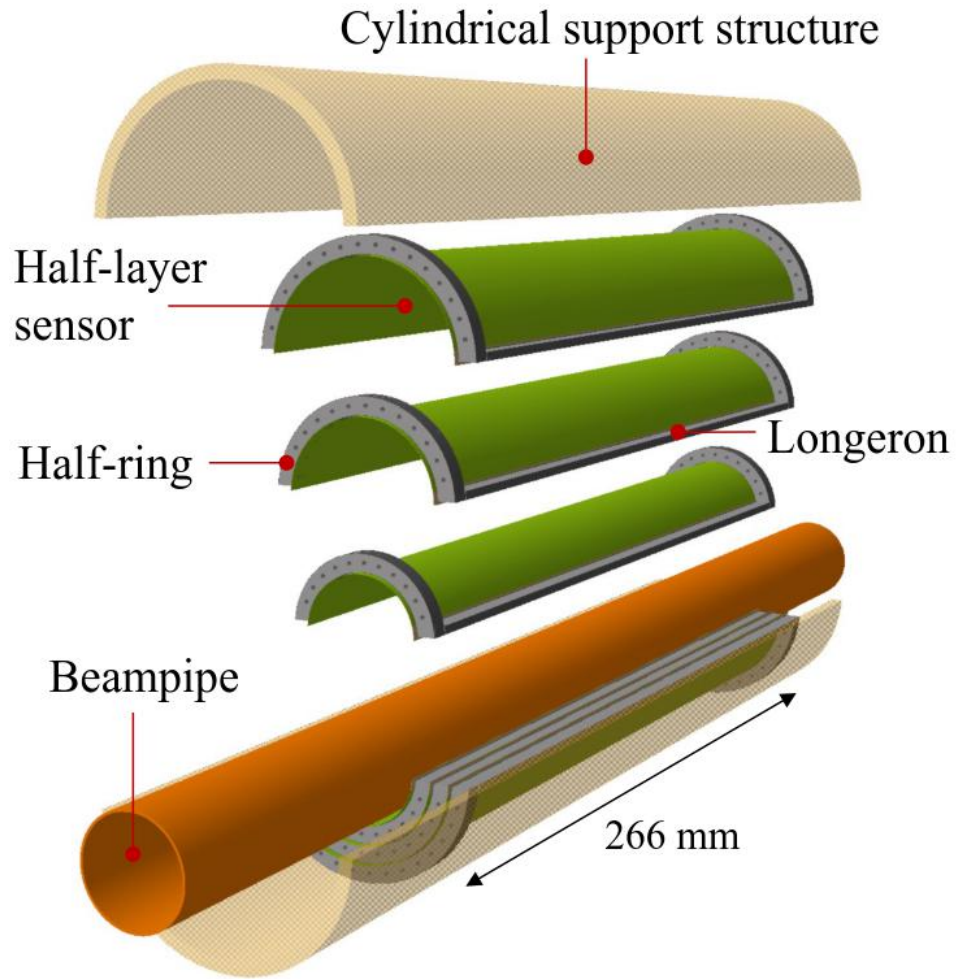
ITS3 detector



ITS3 detector



ITS3 detector

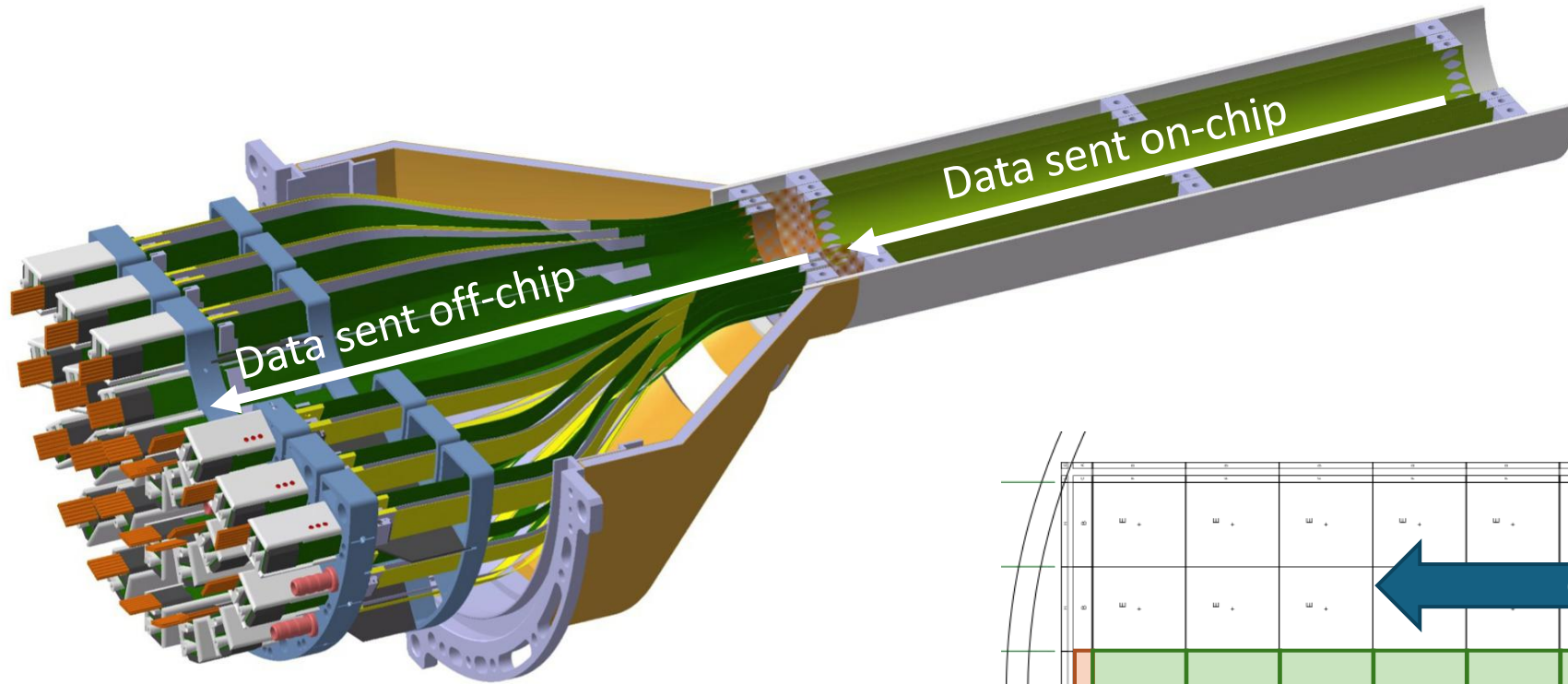


Manufacturing defects can kill an entire sensor

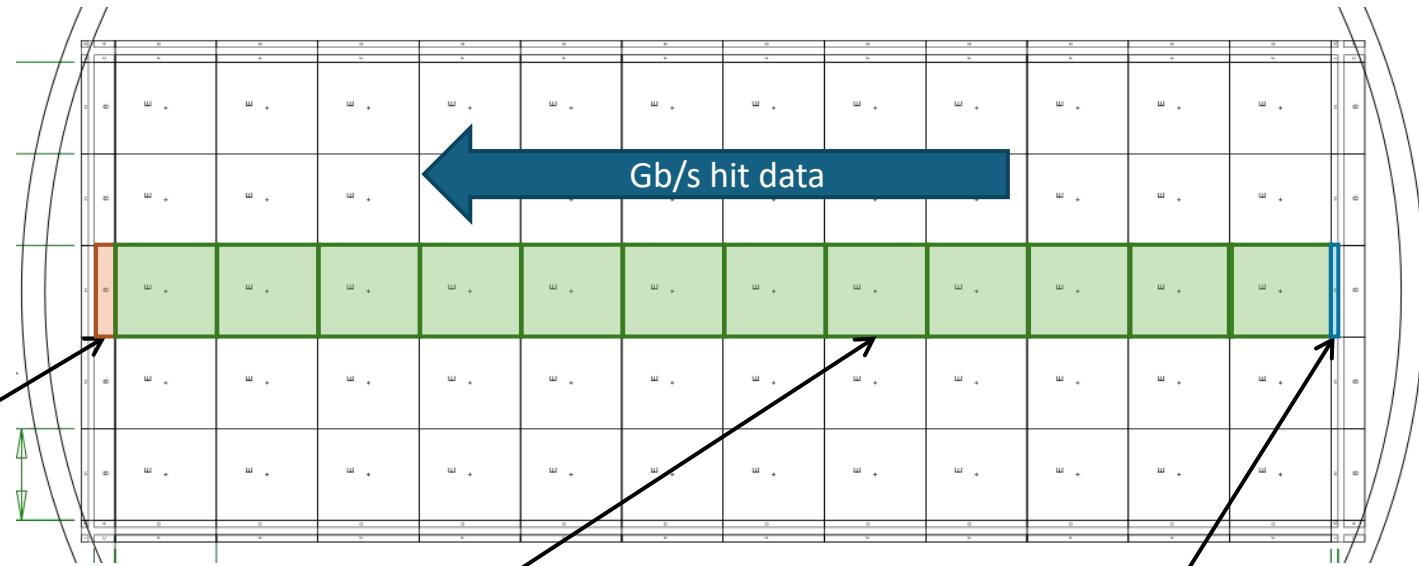
high yield is required

* see Gregor Eberwein's talk on how interesting these type of faults can be

ITS3 detector



4.4 MHz/cm² particle rate

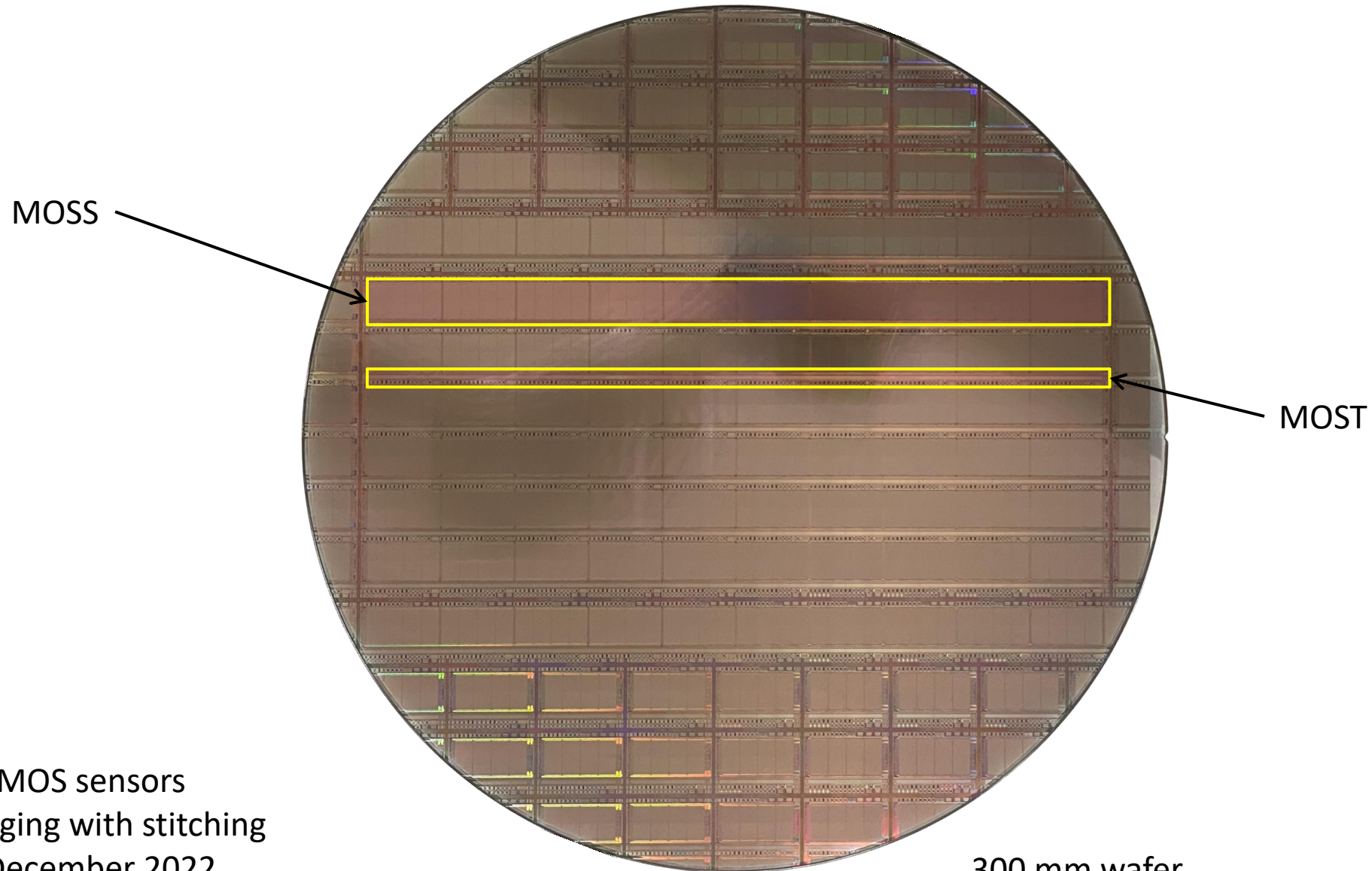


power pads
I/O pads
Gb/s offchip transmitters

sensitive area
readout circuitry

power pads

Wafer scale stitched pixel sensor prototypes



ER1 wafer
Monolithic CMOS sensors
TPSCo65 imaging with stitching
Submission December 2022

300 mm wafer

MOSS

14 mm

259 mm



Study yield and uniformity of large sensing areas
Characterization of pixel frontends

Enlarged spacing design
Coarse power modularity

Two different goals

Two different approaches regarding defects

Study detach of pixel groups from the global power grid via switches
Gb/s on-chip data transmission

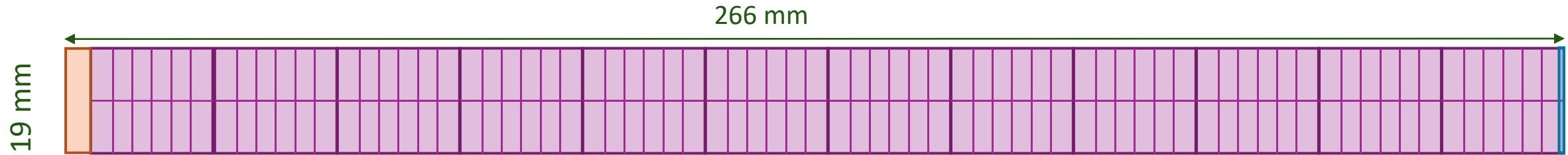
Minimum spacing design
Fine power modularity

MOST

2.5 mm



MOSAIX is the full size, fully functional, stitched sensor prototype for the ITS3

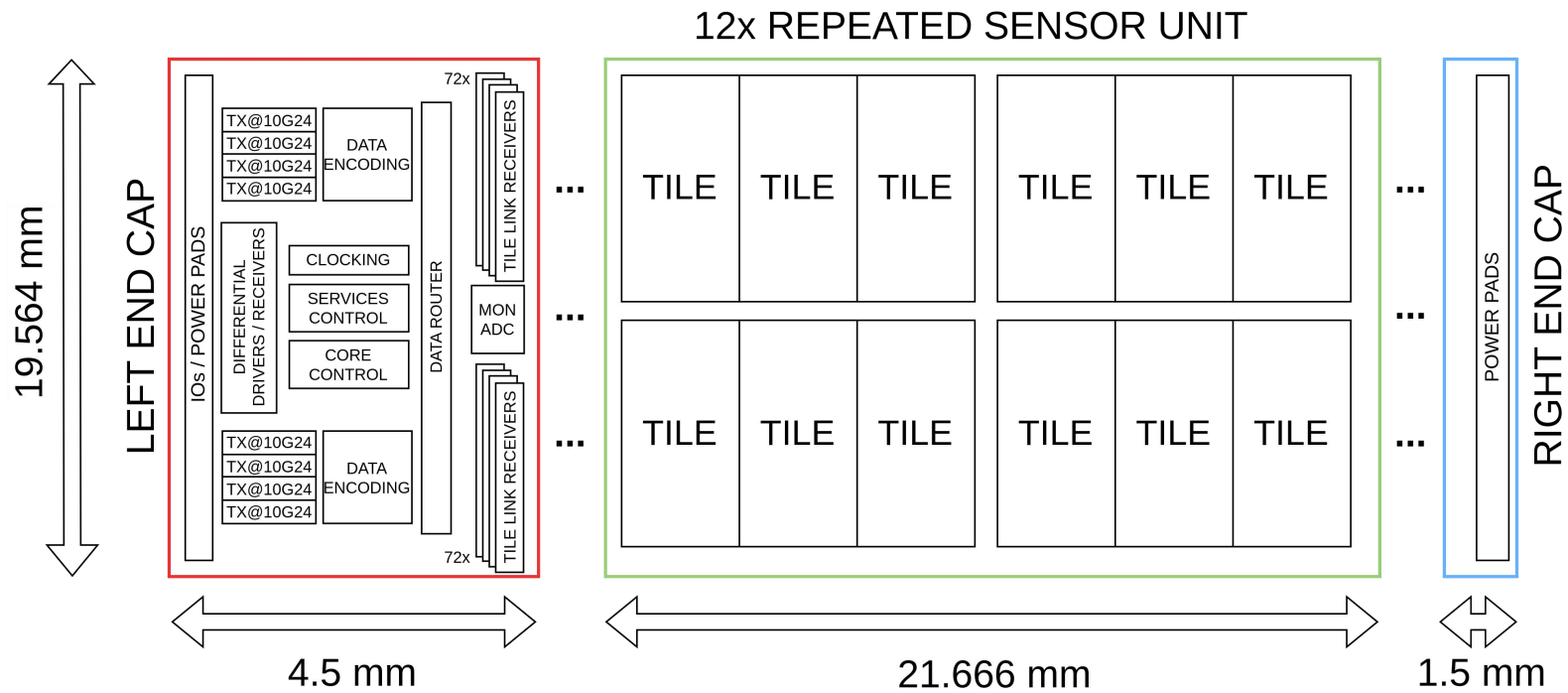
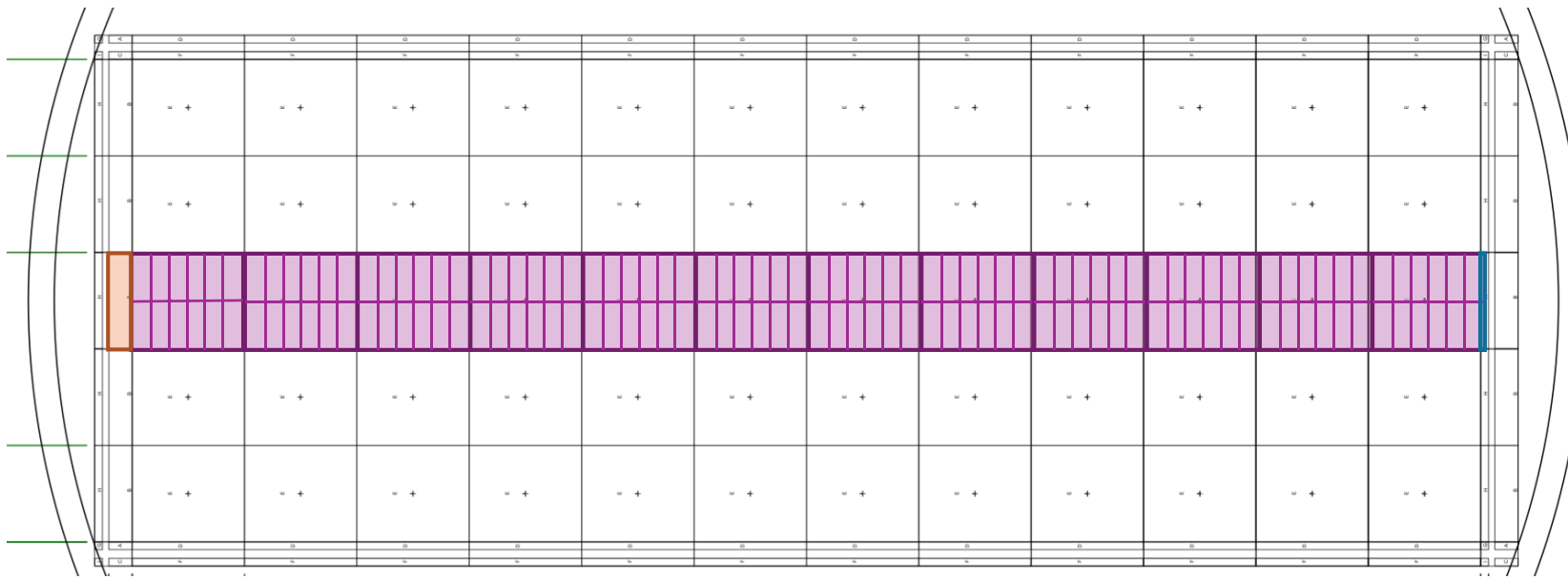


93 % sensitive region
 0.7 % sensor area modularity
 144 tiles (independent units)

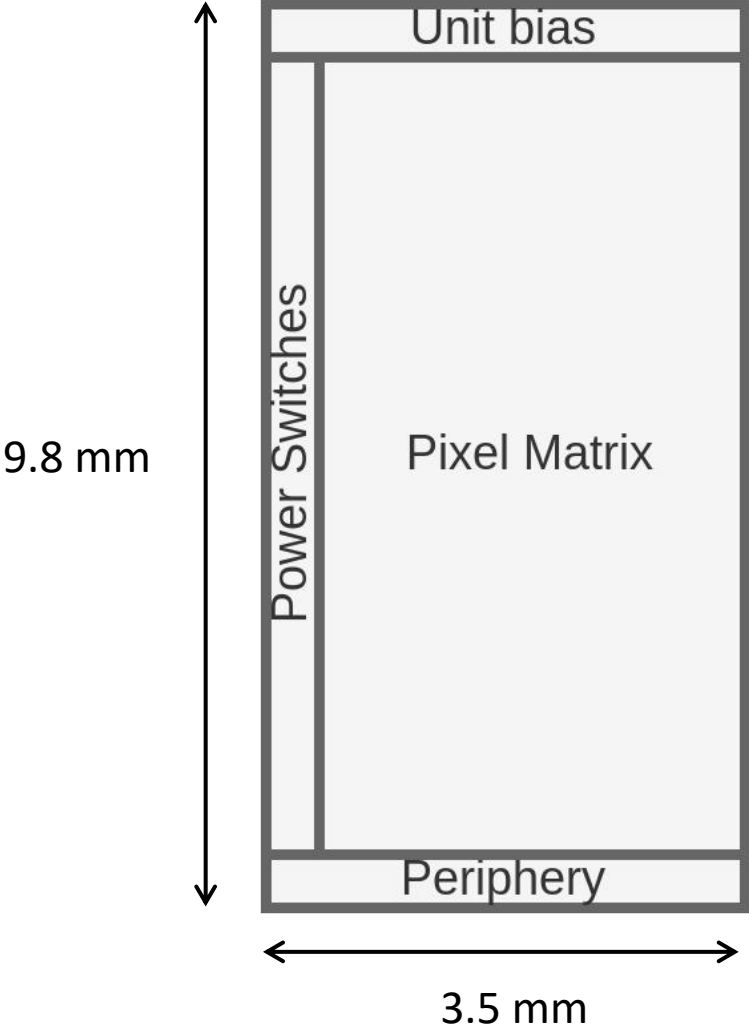
10^{13} NIEL (1 MeV neq cm^{-2})
 10 kGray TID
 Triple modular redundancy

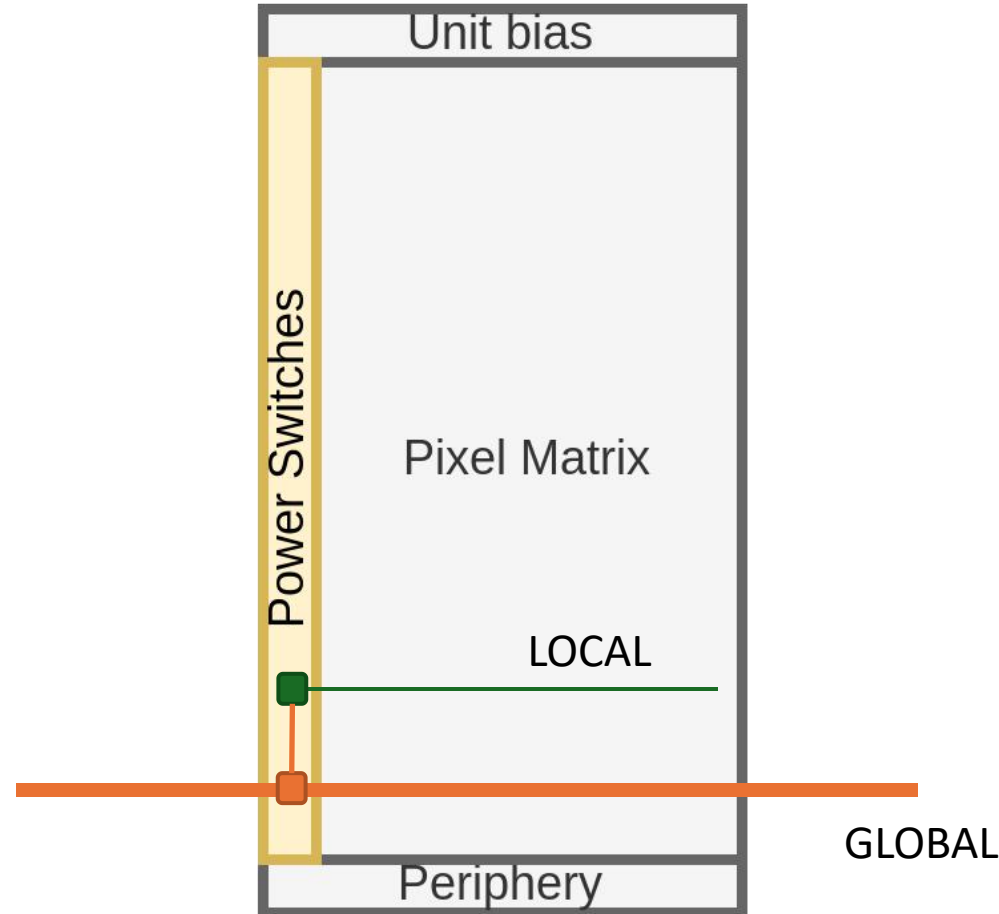
4.4 MHz/ cm^2 particle rate
 30.72 Gb/s off-chip data transmission
 minimum 2 μs integration time
 < 40 mW/ cm^2

20.8 x 22.8 μm^2 pixel size
 Detection Efficiency > 99 %
 Fakehit rate < 0.1 $\text{pixel}^{-1}\text{s}^{-1}$



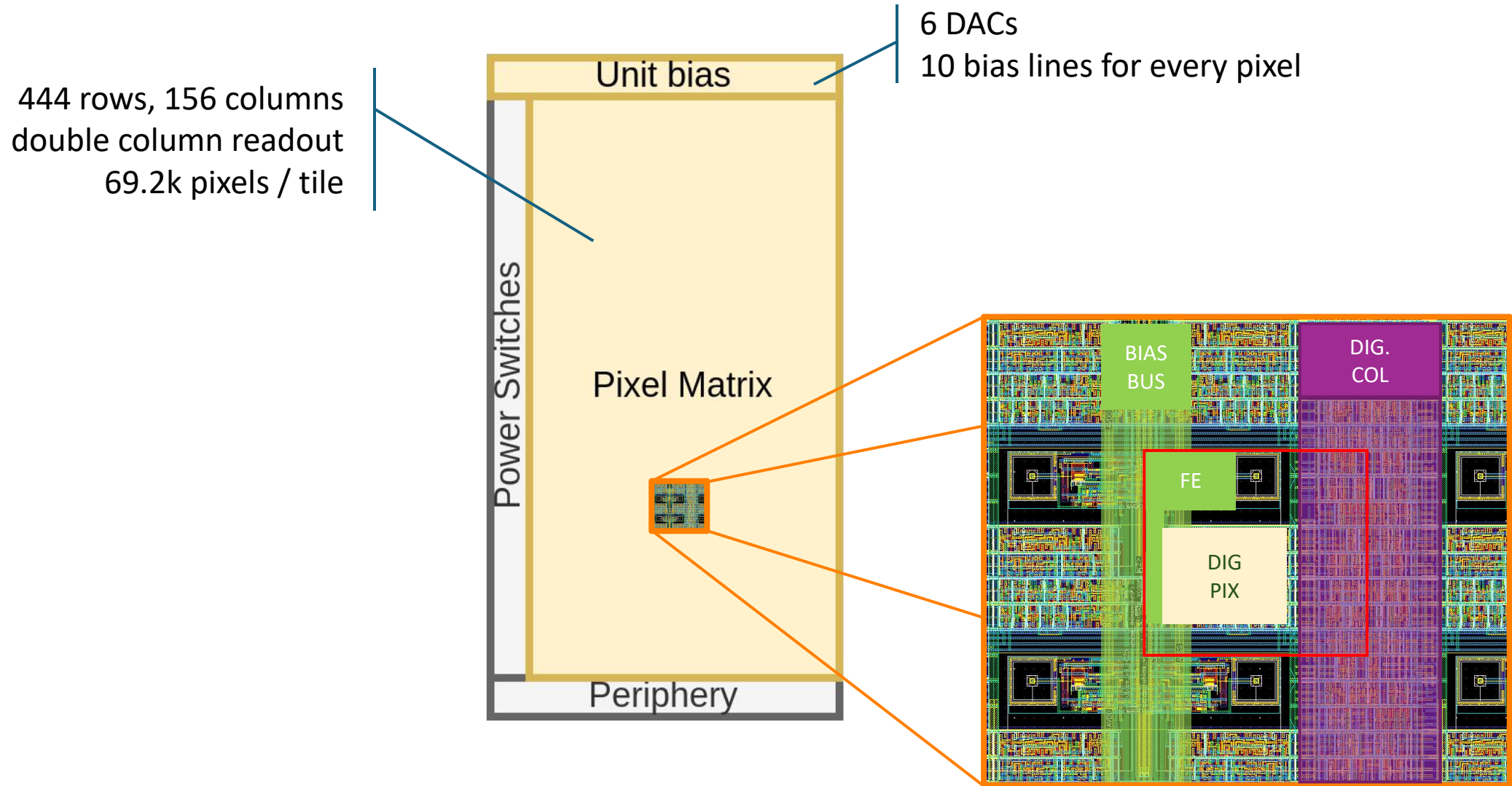
Tile = independent sensor unit



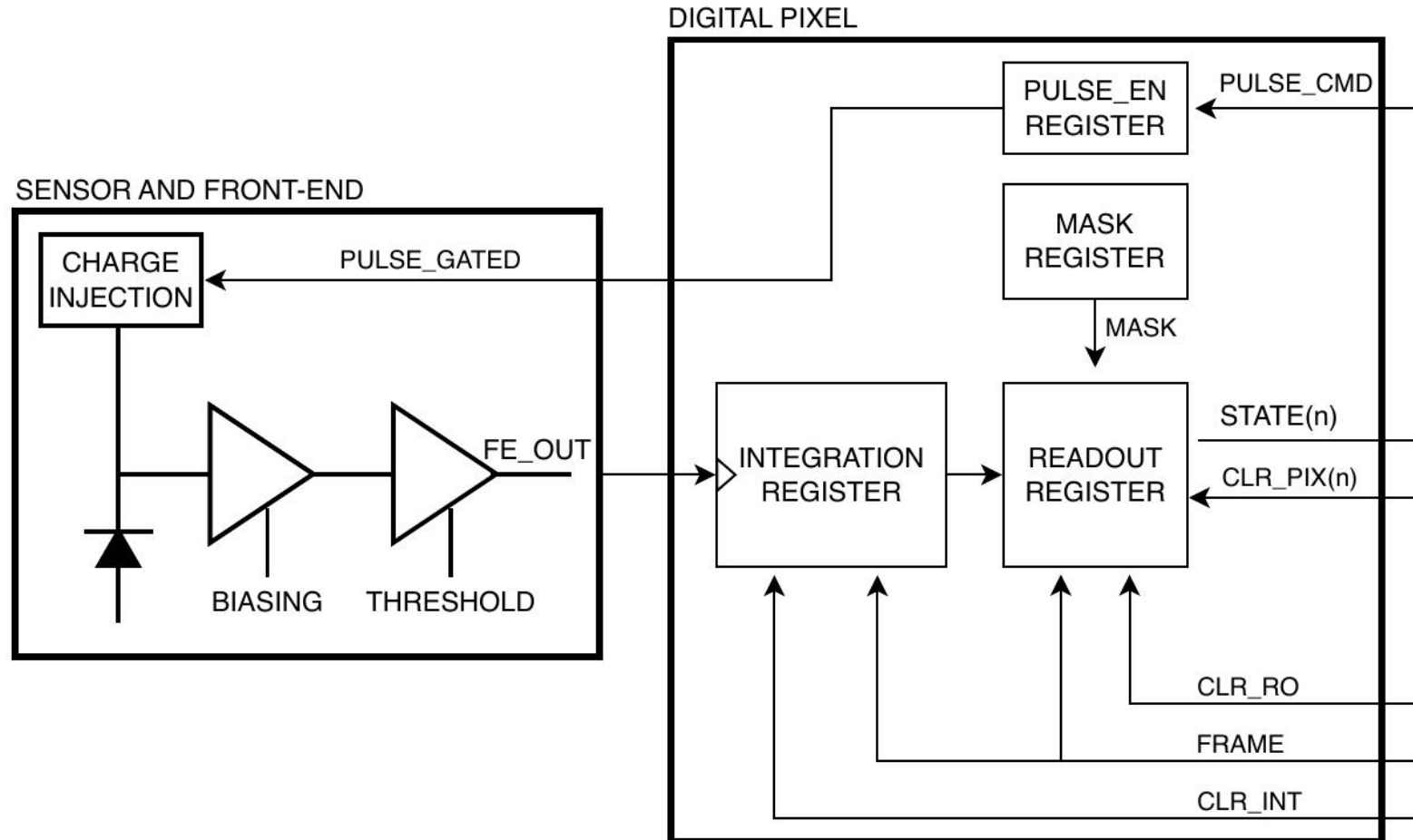


power switches allow to connect the tile to the global power domain

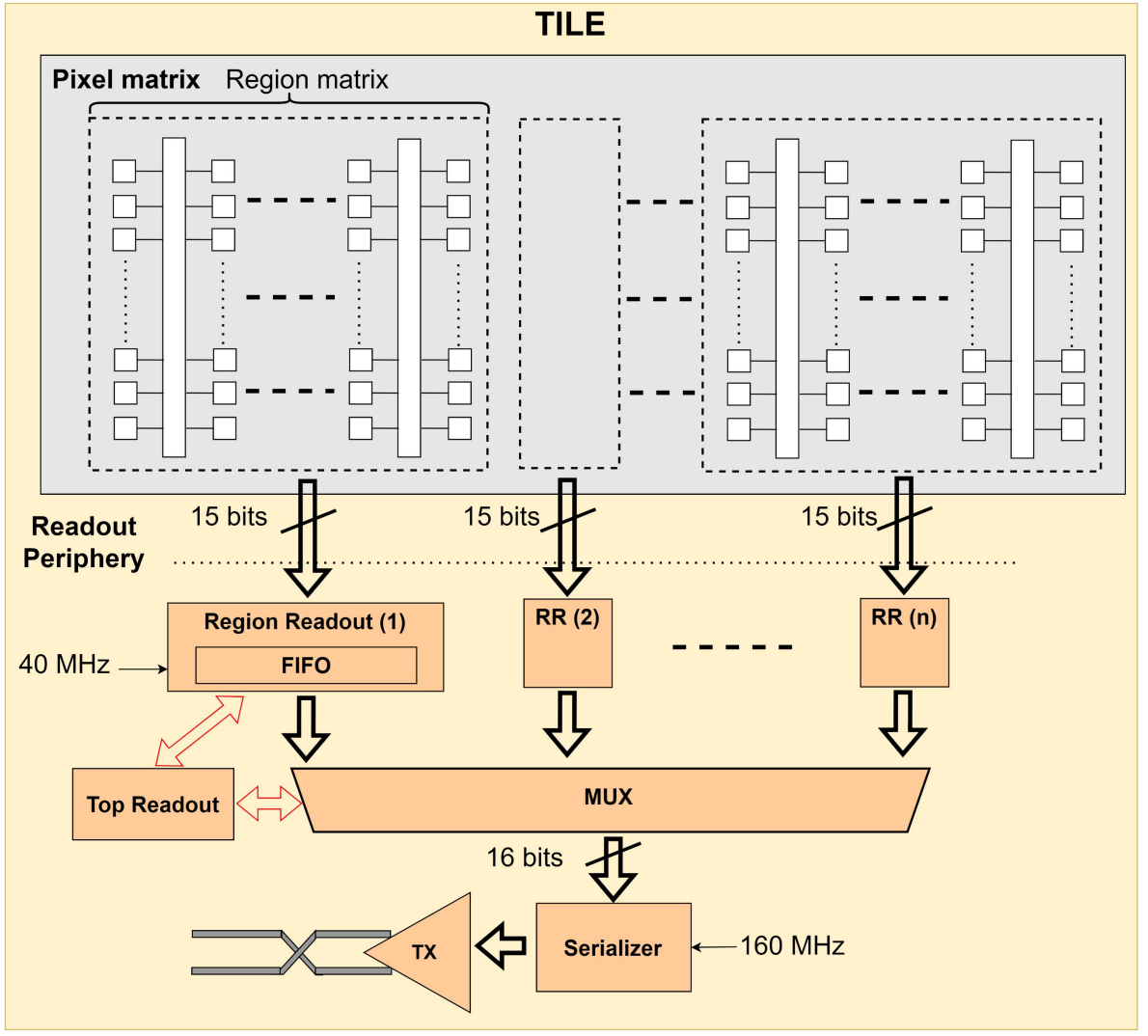
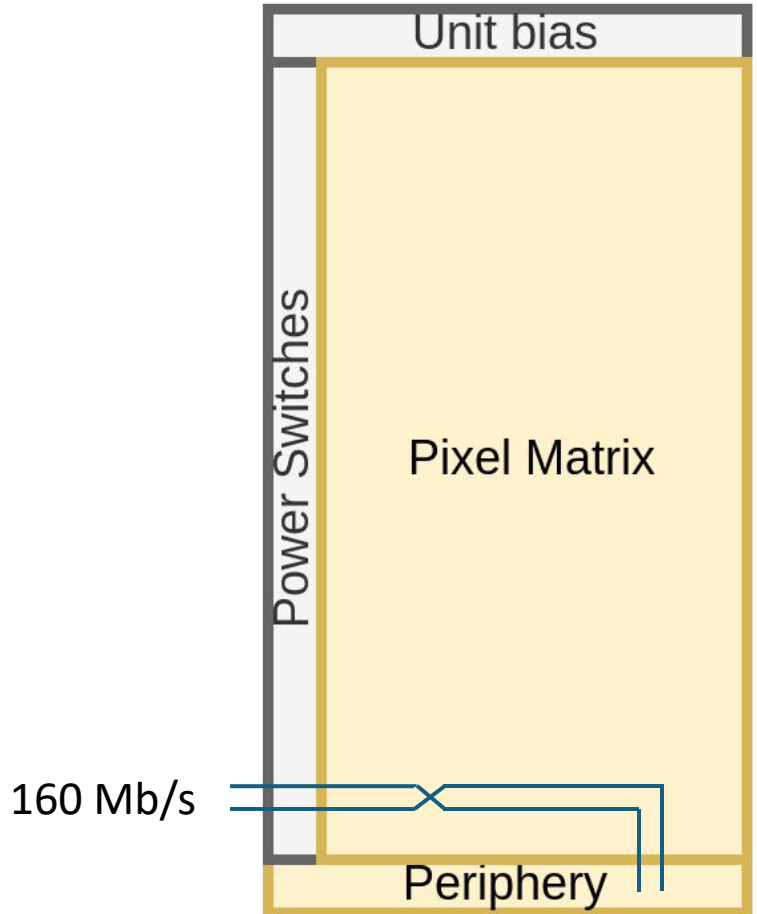
* see Szymon Bugiel's talk on how to reliably distribute power in the MOSAIX chip

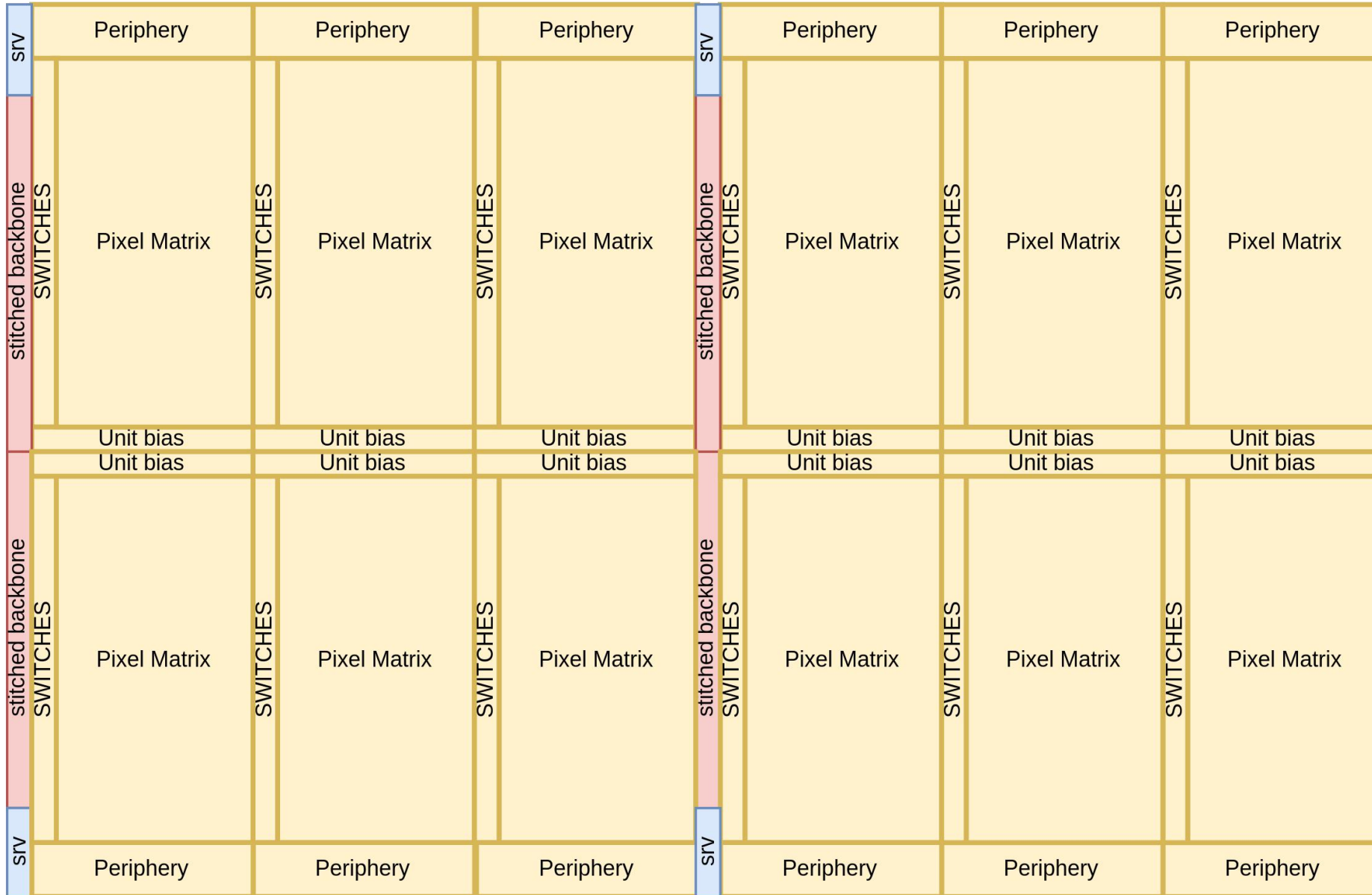


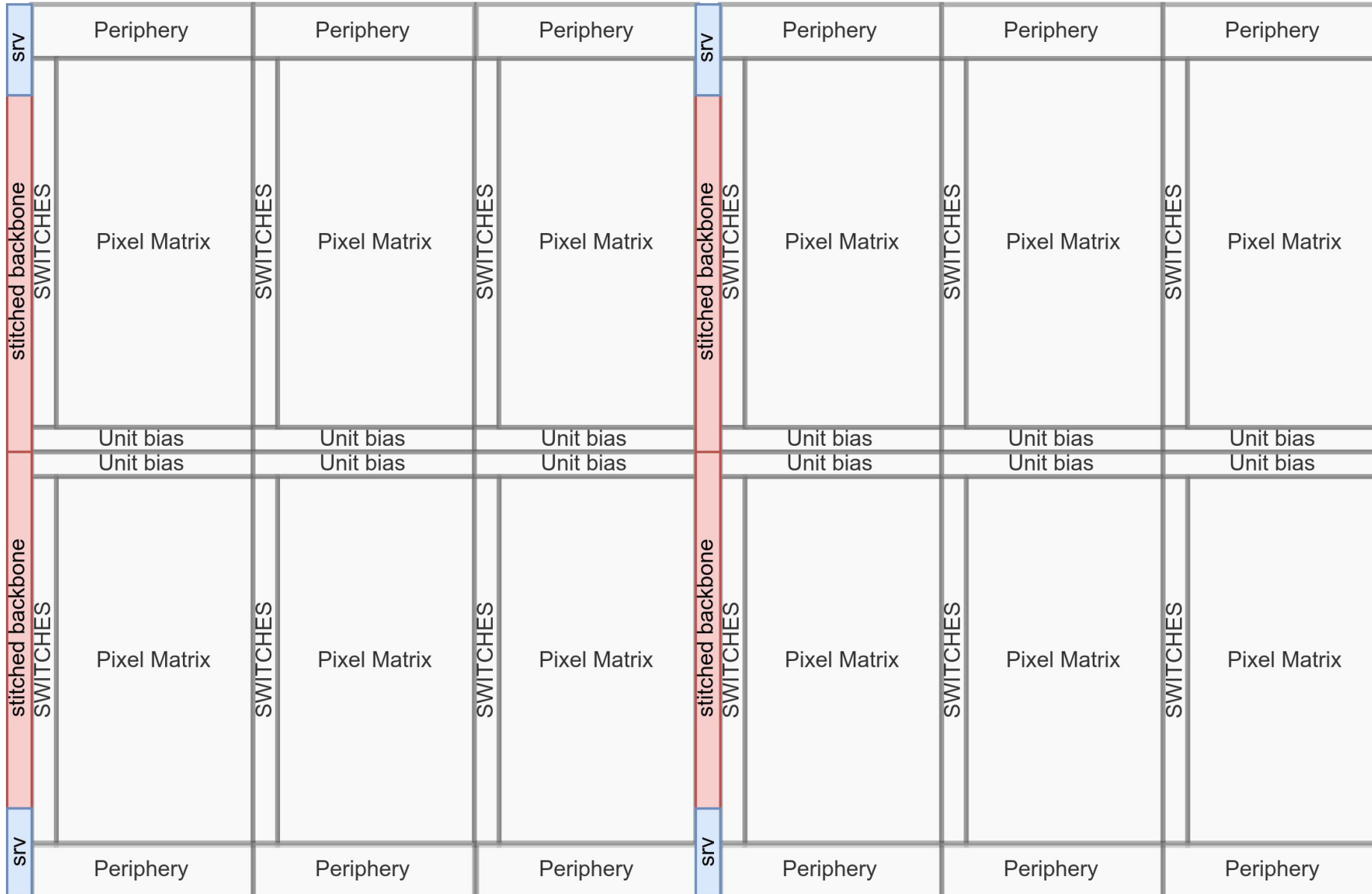
20.8 μm (r-phi) by 22.8 μm (z-axis)



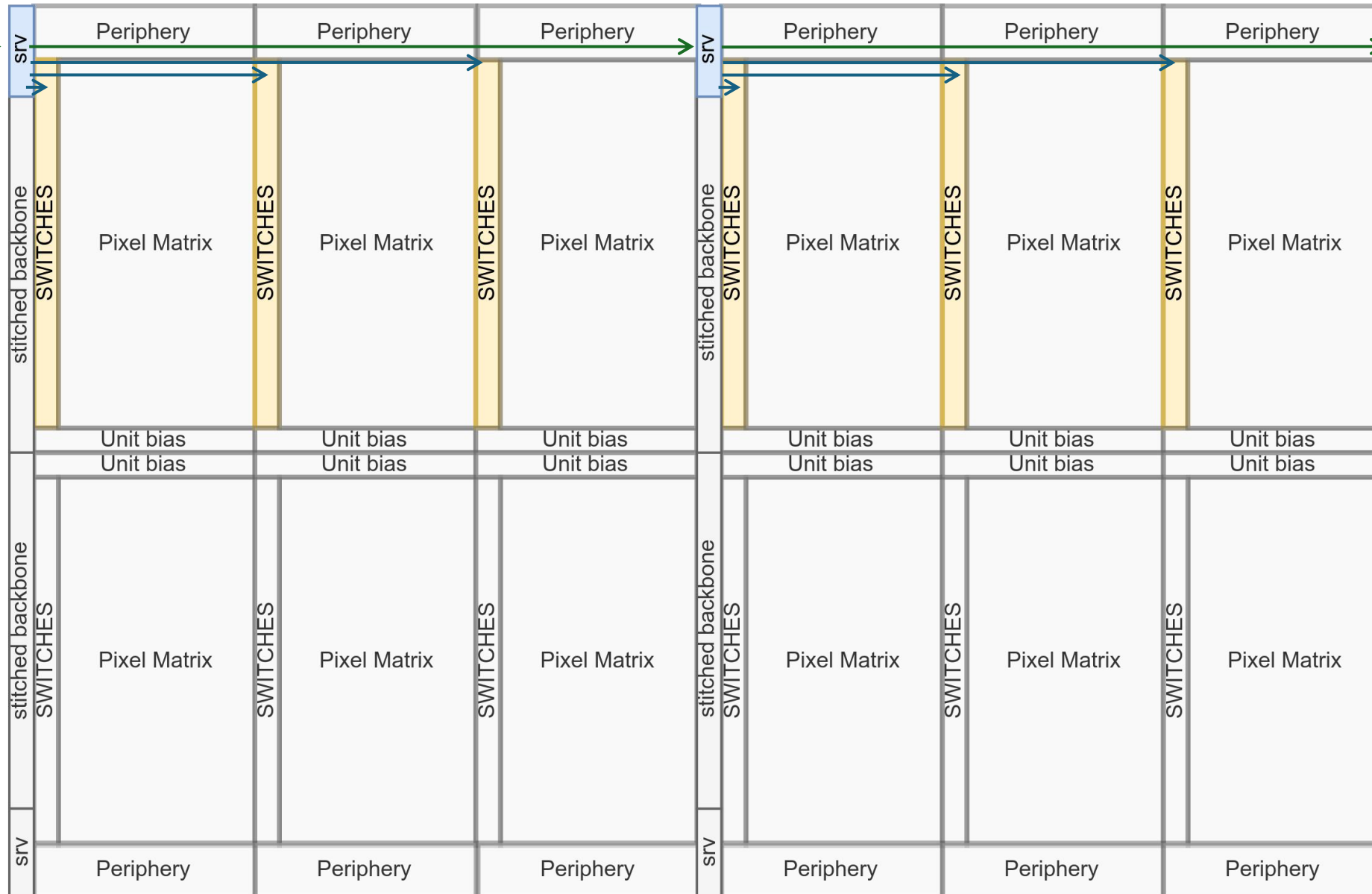
* see Simone Emiliani's presentation on how non-idealities in testing circuitry affects the sensor performance

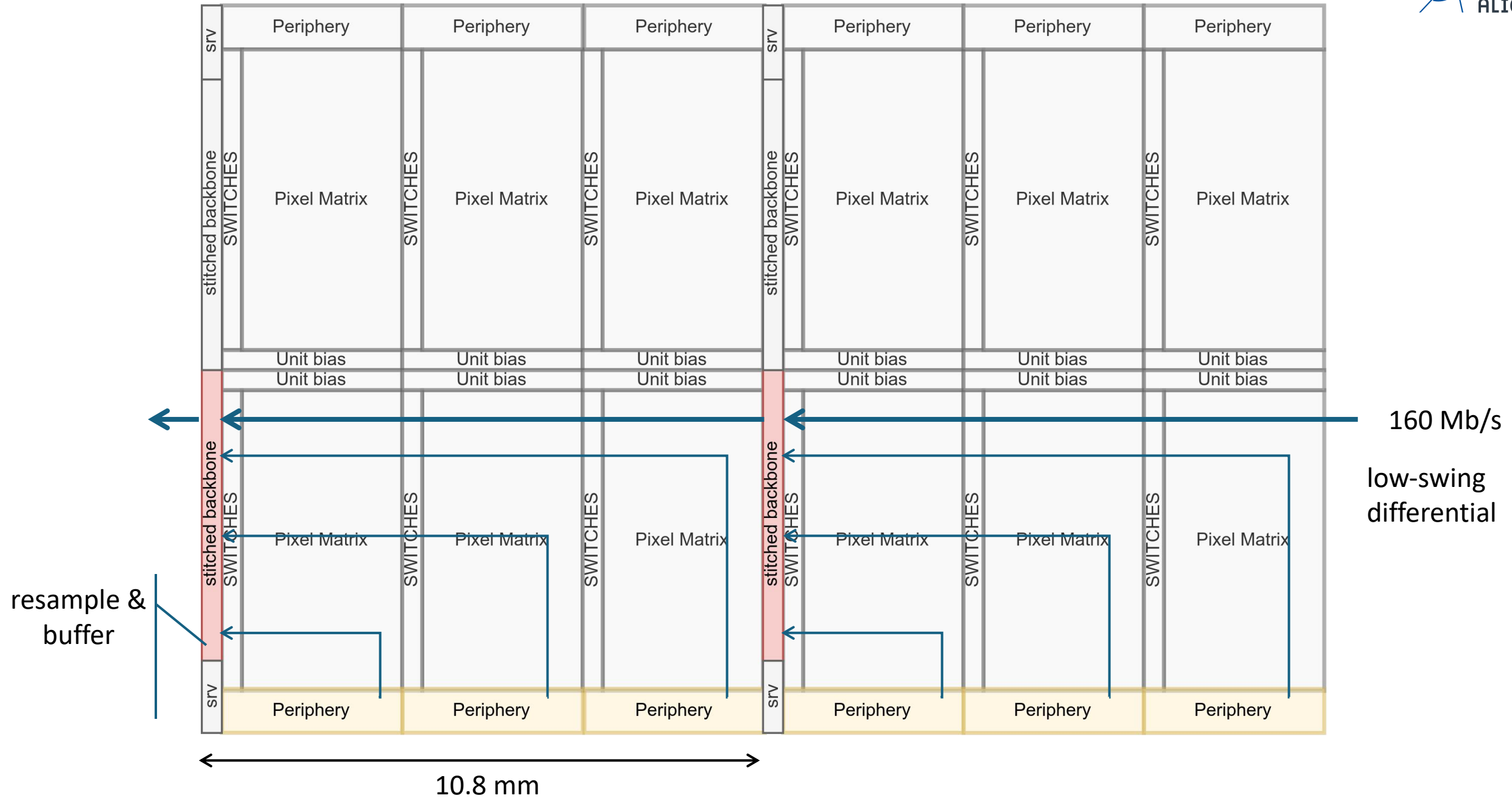






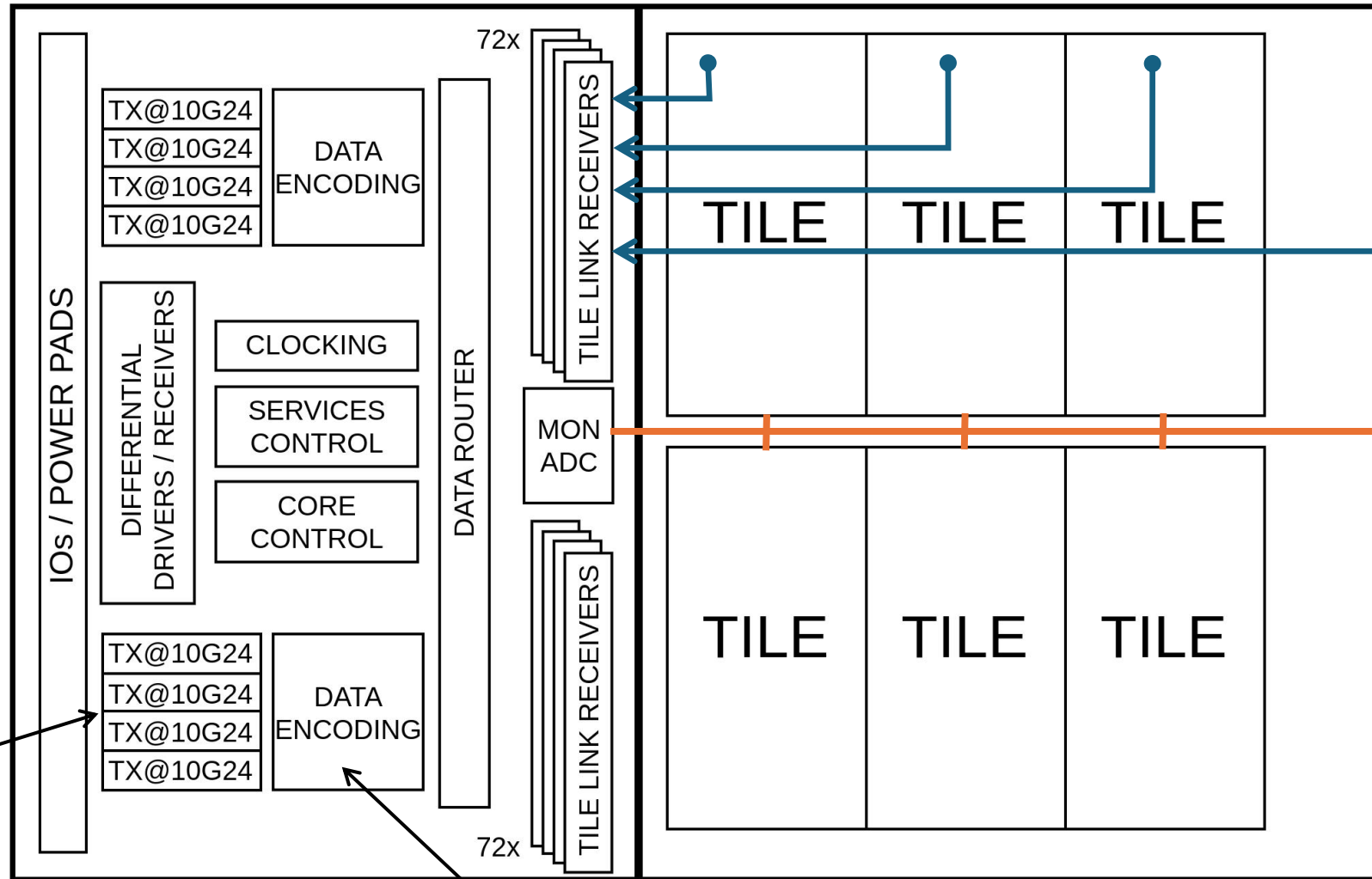
services
5 Mb/s





LEC: data hub

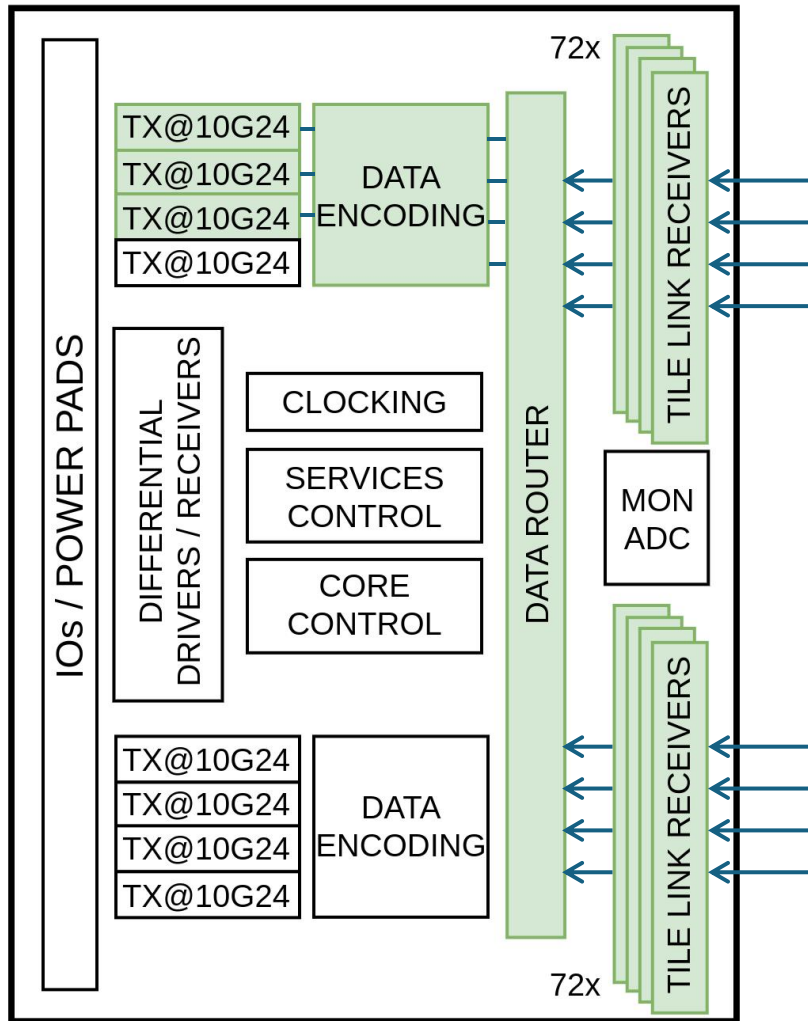
Data path is Versatile Link+ compatible



4 serializers connect to VTRX+

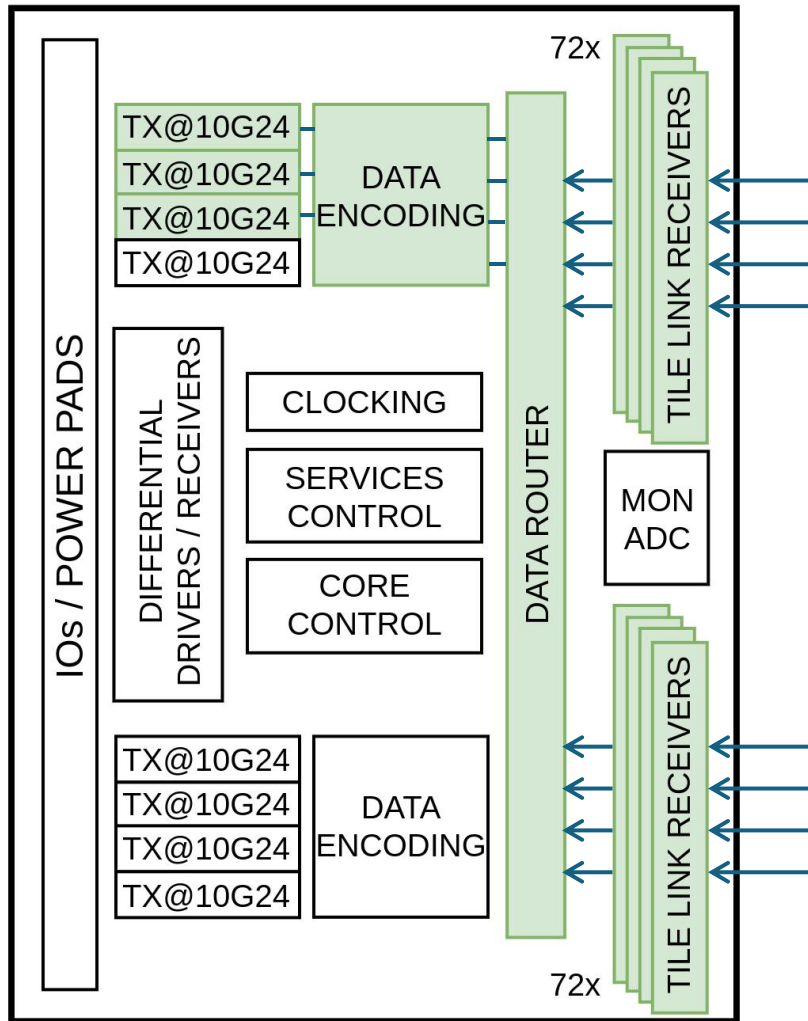
IpGBT frame encoder

[nominal operation]



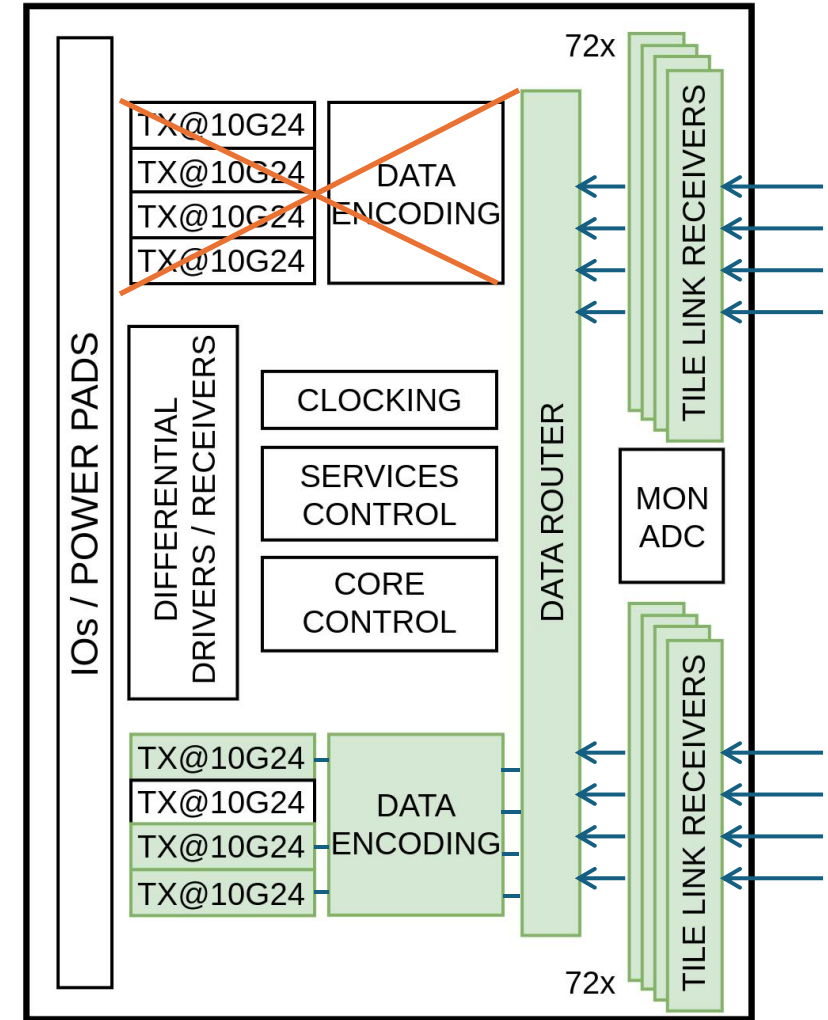
10.24 Gb/s per serializer
3 serializers in use

[nominal operation]



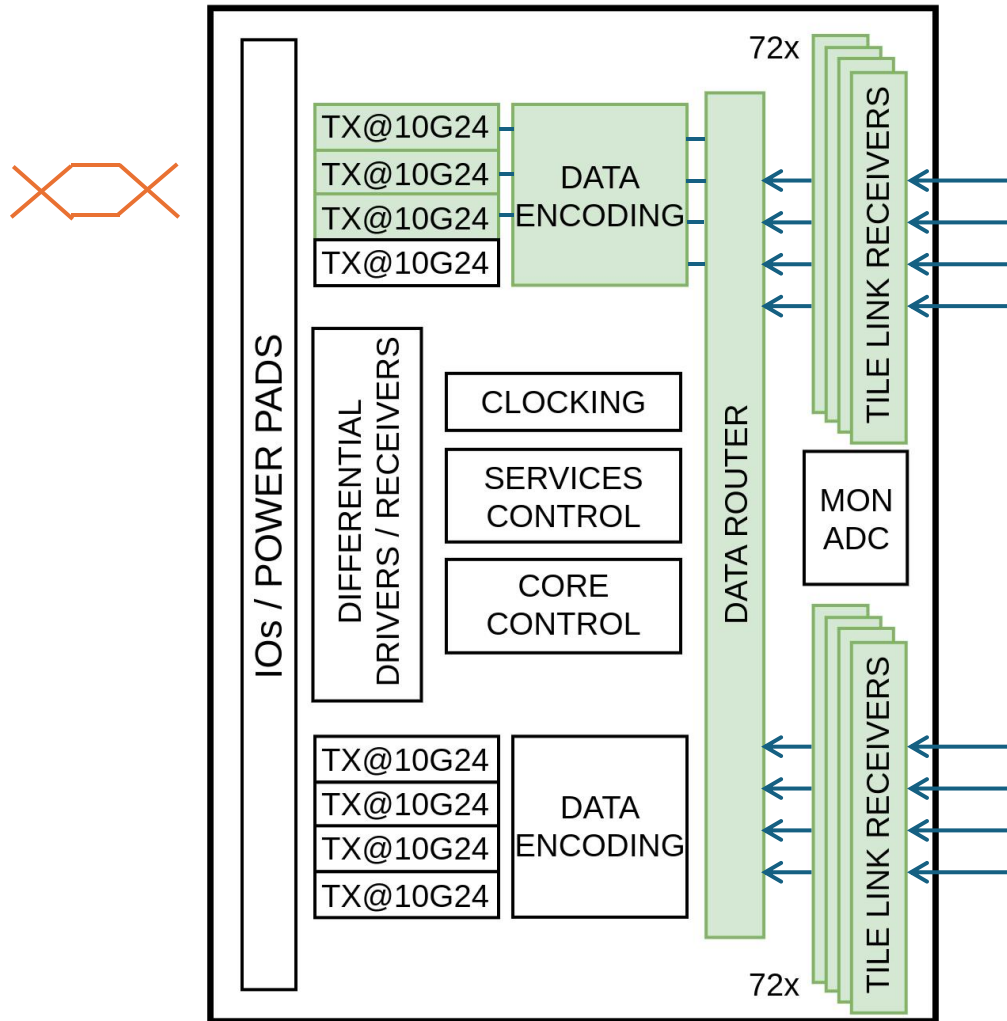
10.24 Gb/s per serializer
3 serializers in use

[in case of fault]



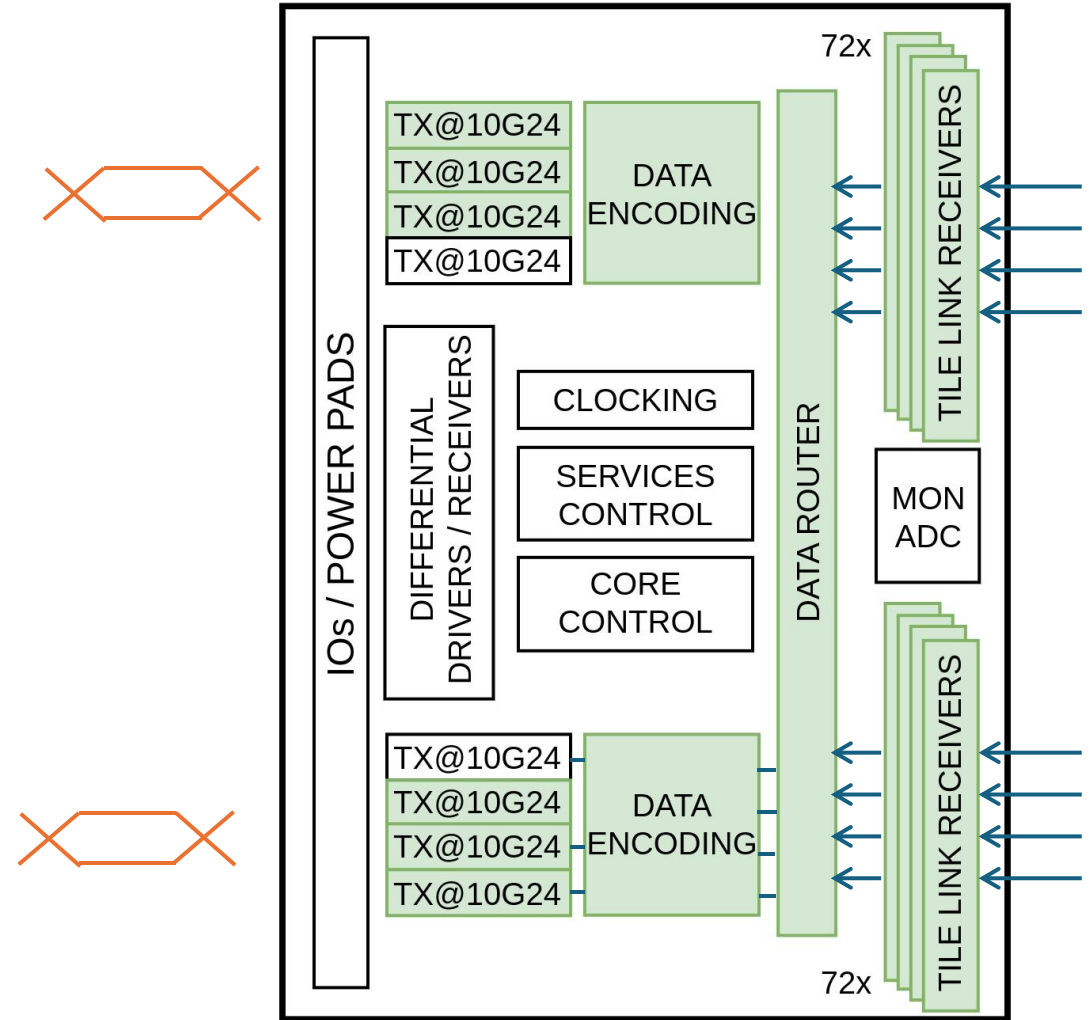
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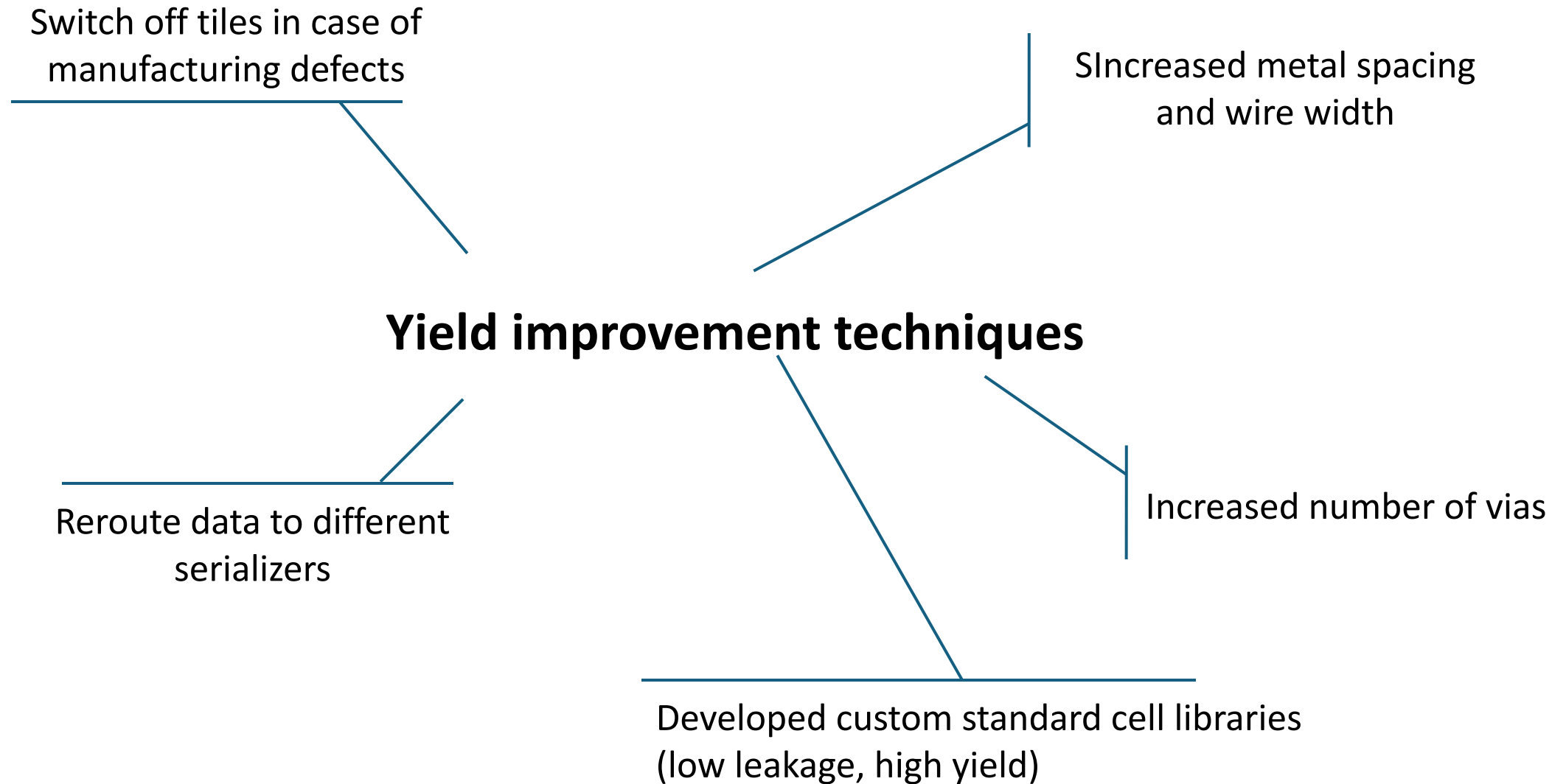
10.24 Gb/s per serializer
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[in case of fault]

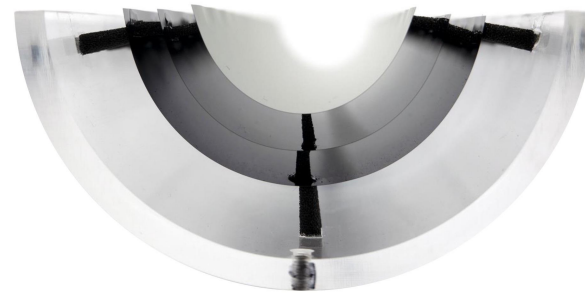


5.12 Gb/s per serializer
6 serializers in use
(bit stretching)

Yield improvement techniques



MOSAIX



Summary

19 mm from the beam pipe

0.07 % X_0 per layer

< 40 mW/cm²

4.4 MHz/cm² hit rate

93% fill factor

26.6 cm x 19 mm

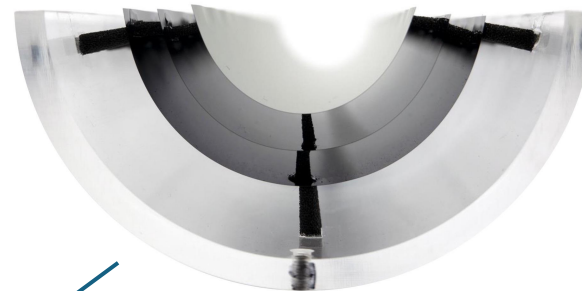
26.6 cm on-chip data transmission

8x 10.24 Gb/s serializers

LpGBT frame encoding

Versatile link+ compatible

MOSAIX



custom layout rules for yield

custom std cells for yield

Summary

MOSAIX entering last design stage

TPSCo65nm imaging with stitching

9.97 million pixels per segment

0.7% sensor area granularity

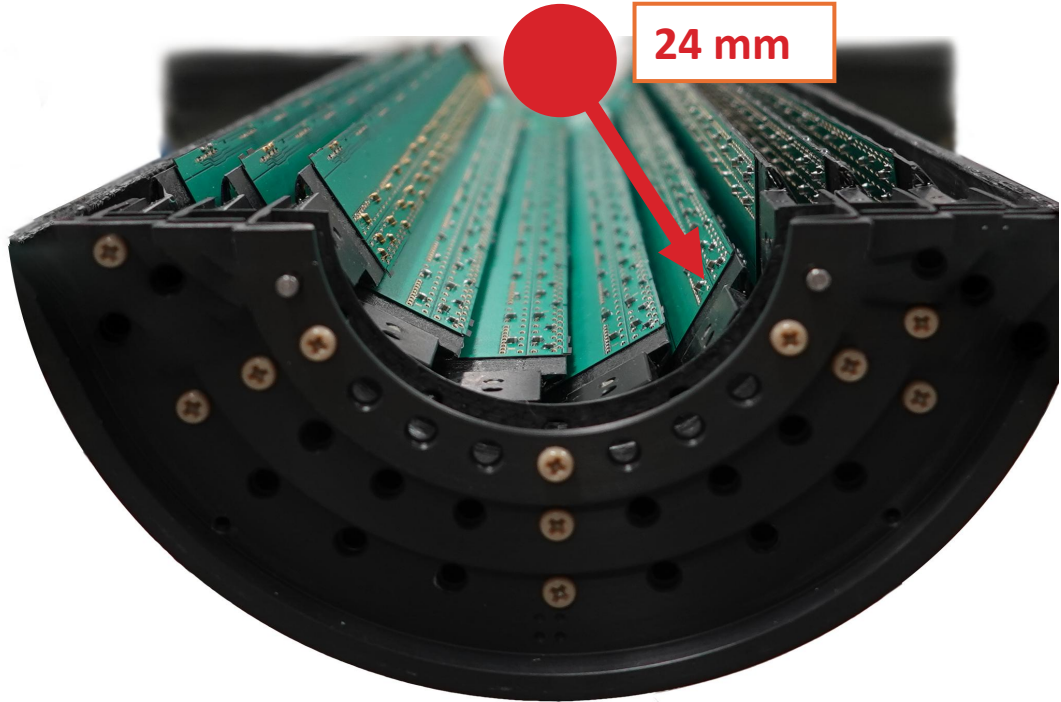
20.8 x 22.8 μm^2 pixel size

Unprecedented in the HEP community!



ALICE

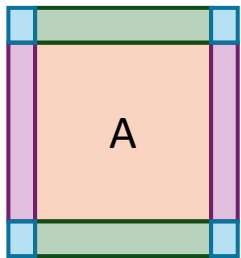
What can we do better?



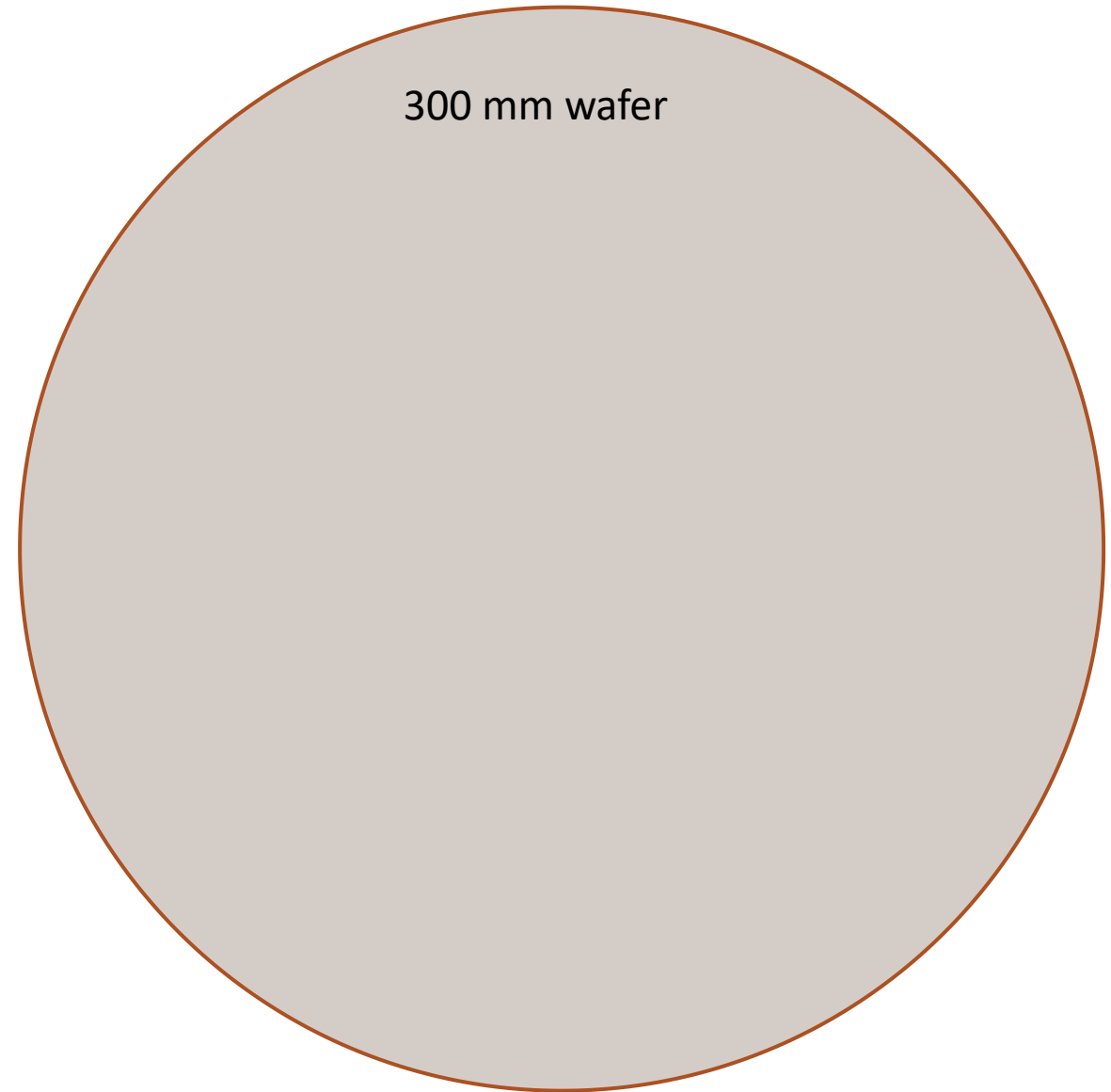
24 mm from the beam pipe
0.35 % X_0 per layer

How to design a wafer scale bent pixel detector?

Max reticle size



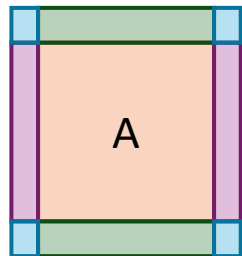
A = sensitive area



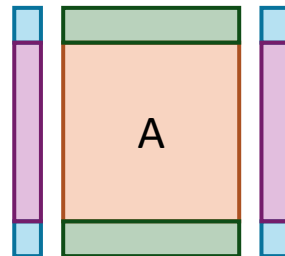
How to design a wafer scale bent pixel detector?

Only possible if the technology allows stitching

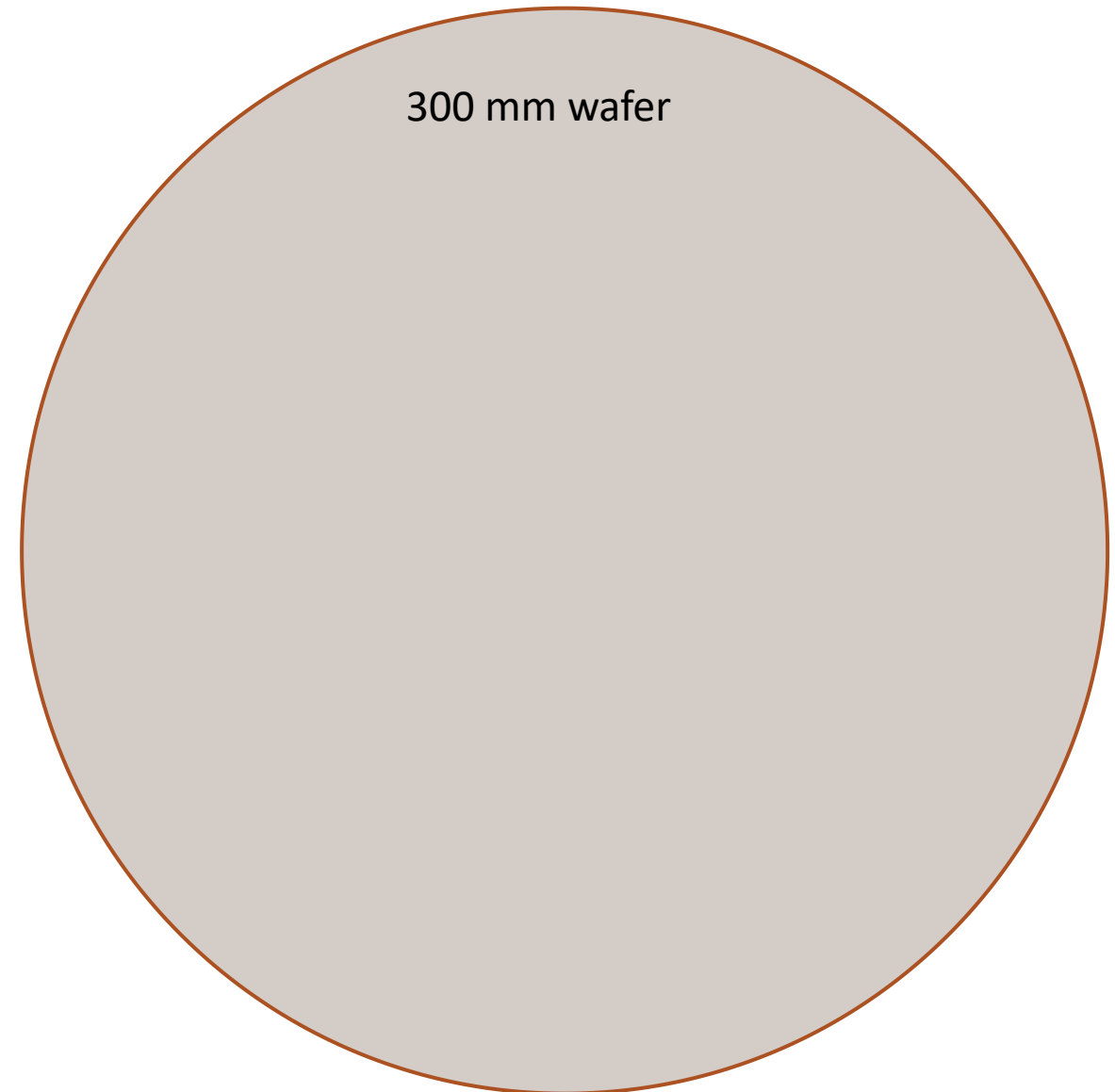
Max reticle size



split design

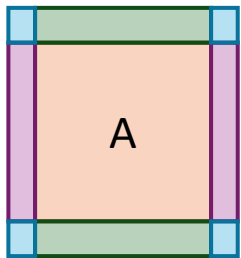


A = sensitive area

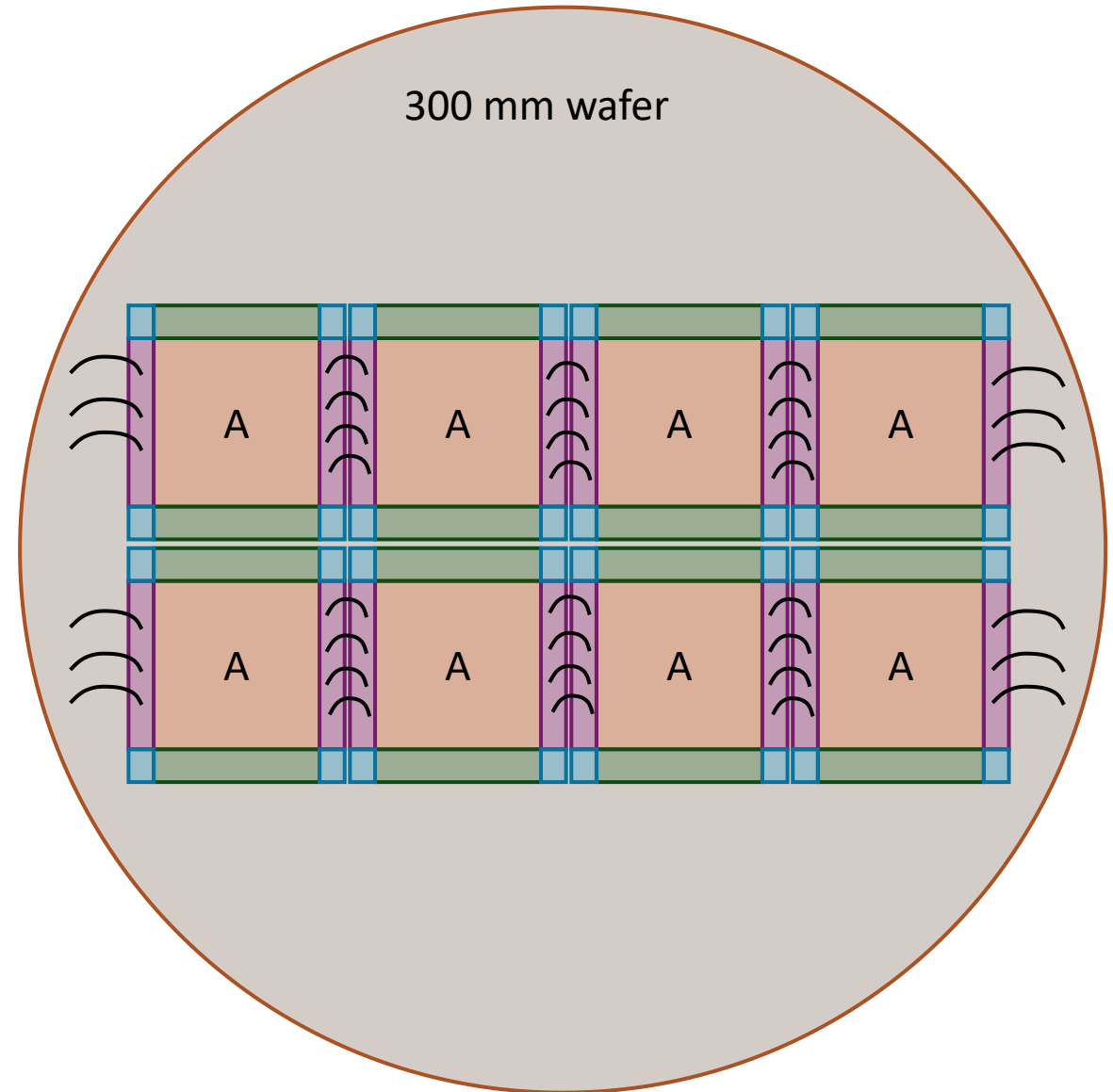


How to design a wafer scale bent pixel detector?

Max reticle size



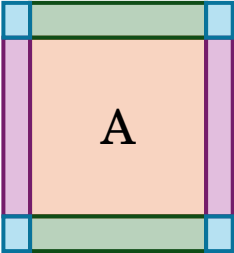
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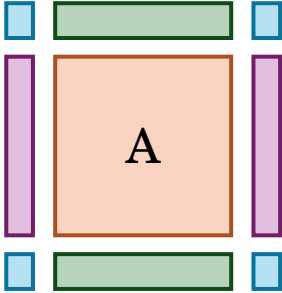
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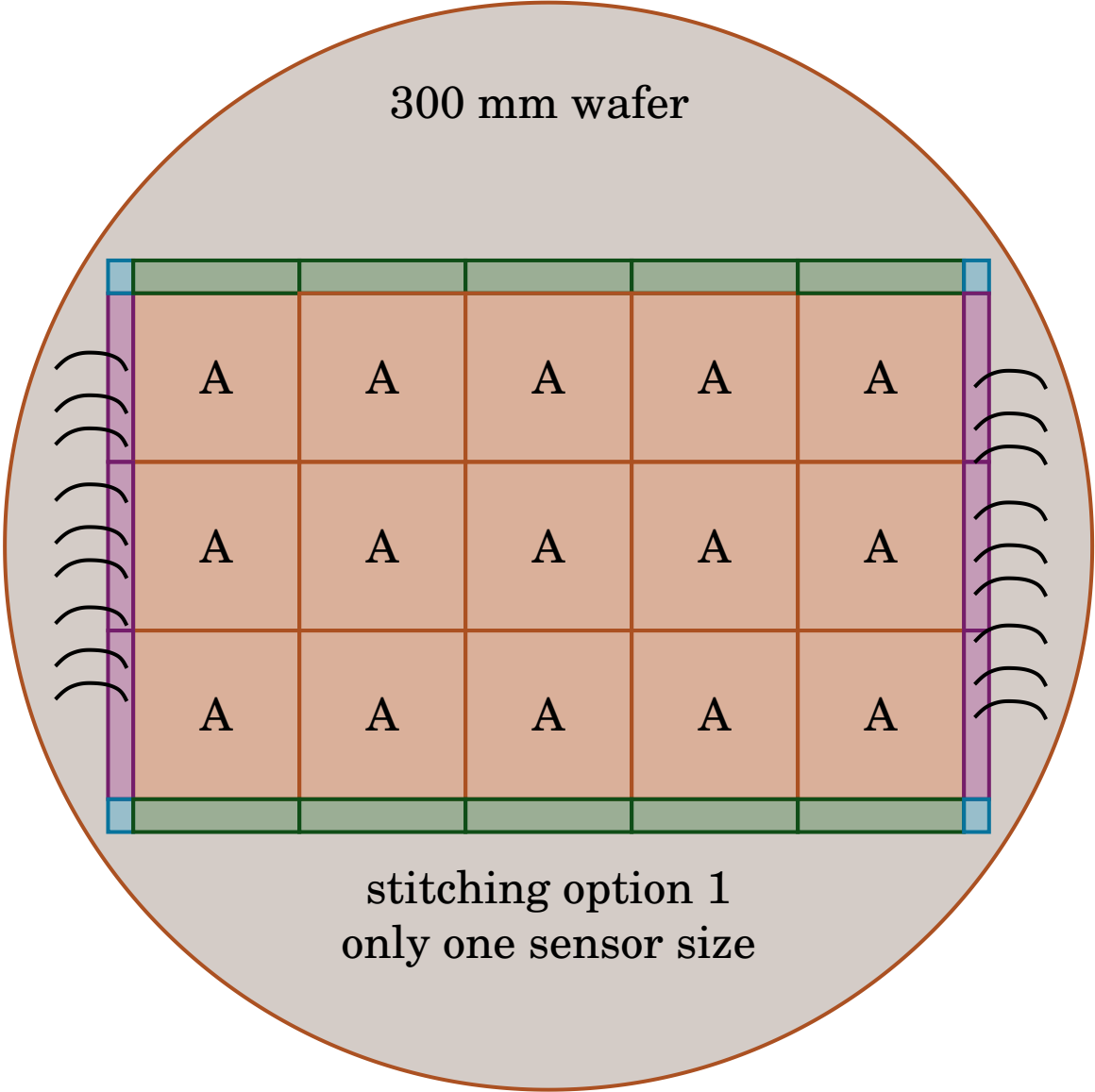
Max reticle size



split design



A = sensitive area



259 mm

MOSS

14 mm



Two different goals

Two different approaches regarding defects

MOST

2.5 mm



Tile = independent sensor unit

4.4 MHz/cm² particle flux

Continuous trigger-less readout

Integration periods of minimum 2 μs

Hits collected in time stamped packets

160 Mb/s low-swing differential data transmission

